

产品简介

ZDH9098 低噪声放大器具有低噪声、高增益、高线性度的特点，且内部集成了 Bypass 模式功能。该器件的工作频率为 200MHz~4500MHz，宽工作电压 3.0V~5.0V。

ZDH9098 产品针对无线基础设施进行了优化设计，采用小型化的 8 脚 DFN2x2 封装，具有很好的可靠性和经济性。

典型应用场景

- LTE / WCDMA / CDMA / GSM 接收
- 4G/5G 移动基站
- 北斗/GPS/GLONASS/GALILEO 导航接收
- TDD 或 FDD 系统
- 光接收系统

极限最大额定值

参数	数值
存储温度	-65°C~+150°C
工作温度	-55°C~+125°C
极限电压 (VDD)	6V
最大输入功率 (RFIN)	+22dBm

工作状态控制逻辑表

状态	BYP	VSD
LNA 开, Bypass 关	0	0
LNA 关, Bypass 关	0	1
LNA 关, Bypass 开	1	X

“0”：0~0.6V

“1”：1.2V~VDD

“X”：无关

开关时间

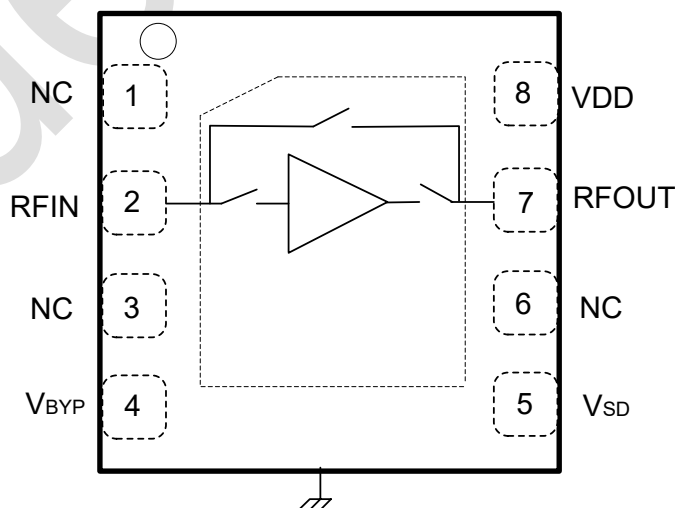
状态	时间 (ns)
Bypass—OFF—ON	1740
Bypass—ON—OFF	352
Bypass—LNA	1330
LNA—Bypass	49

产品特点

- 3V~5V 宽工作电压，典型电流
47mA @ 3.3V, 71mA @ 5V
- 典型增益：20dB @ 1500MHz、VDD=3.3V；
20dB @ 1500MHz、VDD=5V
- 典型 OIP3：30dBm @ 1500MHz、VDD=3.3V；
34dBm @ 1500MHz、VDD=5V
- 典型 P1dB：16dBm @ 1500MHz、VDD=3.3V；
19dBm @ 1500MHz、VDD=5V
- 输入/输出 50Ω 阻抗匹配
- 绿色无铅 8 脚 DFN2x2 封装

 本产品符合所有相关法规且不含卤素。

管脚示意图 (Top View)



管脚号	名称	说明
1,3,6	NC	悬空或者接地
2	RFIN	射频输入
4	VBYP	旁路控制
5	VSD	关断控制
7	RFOUT	射频输出
8	VDD	电源电压
9	EPAD	GND

**电气参数 (VDD=3.3V、108MHz-174MHz)**

低噪放模式测试条件: VDD = +3.3V, Iq=48mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值			单位
频率	108	136	174	MHz
小信号增益 (Gain)	23.1	23.5	23.2	dB
输入回损(S11)	-10.4	-9.4	-9.4	dB
输出回损(S22)	-9.8	-19.3	-13.9	dB
反向隔离(S12)	-30.2	-30.3	-30.5	dB
噪声系数 (NF)	0.5	0.7	0.6	dB
输出功率 1dB 增益压缩点 (P1dB)	13.26	14.11	13.74	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	29.3	29.5	30.0	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值			单位
频率	108	136	174	MHz
插入损耗(S21)	-1.6	-1.2	-1.4	dB
输入回损(S11)	-9.6	-16.4	-13.2	dB
输出回损(S22)	-10.8	-25.3	-13.6	dB

关断模式测试条件: VDD = +3.3V, Iq=4mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值			单位
频率	108	136	174	MHz
插入损耗(S21)	-27.1	-26	-25.2	dB
输入回损(S11)	-0.6	-0.6	-0.6	dB
输出回损(S22)	-5.1	-8.1	-7.1	dB

**电气参数 (VDD=3.3V、200MHz-2500MHz)**

低噪声模式测试条件: VDD = +3.3V, Iq=45mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	500	1000	1500	2500	MHz
小信号增益 (Gain)	23	21	20	17	dB
输入回损(S11)	-9	-9	-11	-10	dB
输出回损(S22)	-12	-7	-7	-11	dB
反向隔离(S12)	-28	-30	-29	-34	dB
噪声系数 (NF)	0.6	0.6	0.8	1.2	dB
输出功率 1dB 增益压缩点 (P1dB)	15	16	16	15	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	32	29	30	30	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +3.3V, Iq=6mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	500	1000	1500	2500	MHz
插入损耗(S21)	-2	-1	-2	-2	dB
输入回损(S11)	-6	-15	-14	-13	dB
输出回损(S22)	-7	-13	-12	-10	dB
输出功率 1dB 增益压缩点 (P1dB)	22	23	23	22	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	39	40	40	36	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	500	1000	1500	2500	MHz
插入损耗(S21)	-24	-25	-24	-23	dB
输入回损(S11)	-0.8	-0.9	-1.5	-2.5	dB
输出回损(S22)	-5	-3	-4	-5	dB

**电气参数 (VDD=3.3V、2500MHz-3500MHz)**

低噪放模式测试条件: VDD = +3.3V, Iq=47mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	2500	2750	3000	3500	MHz
小信号增益 (Gain)	17	17	17	16	dB
输入回损(S11)	-11	-15	-28	-11	dB
输出回损(S22)	-9	-12	-17	-9	dB
反向隔离(S12)	-36	-34	-31	-33	dB
噪声系数 (NF)	1.0	1.2	1.3	1.7	dB
输出功率 1dB 增益压缩点 (P1dB)	16	15	14	13	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	32	34	36	34	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +3.3V, Iq=6mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	2500	2750	3000	3500	MHz
插入损耗(S21)	-2	-2	-2	-2	dB
输入回损(S11)	-13	-14	-12	-15	dB
输出回损(S22)	-14	-14	-16	-18	dB
输出功率 1dB 增益压缩点 (P1dB)	22	22	22	21	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	37	37	37	31	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	2500	2750	3000	3500	MHz
插入损耗(S21)	-23	-23	-22	-22	dB
输入回损(S11)	-1	-2	-3	-3	dB
输出回损(S22)	-8	-10	-9	-7	dB

**电气参数 (VDD=3.3V、3500MHz-4500MHz)**

低噪放模式测试条件: VDD = +3.3V, Iq=51mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	3500	3750	4000	4500	MHz
小信号增益（Gain）	17	16	16	14	dB
输入回损(S11)	-14	-14	-14	-15	dB
输出回损(S22)	-15	-9	-8	-10	dB
反向隔离(S12)	-35	-32	-34	-34	dB
噪声系数 (NF)	1.5	1.5	1.6	2.2	dB
输出功率 1dB 增益压缩点 (P1dB)	14	13	13	12	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	29	28	28	27	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +3.3V, Iq=6mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	3500	3750	4000	4500	MHz
插入损耗(S21)	-2	-2	-2	-3	dB
输入回损(S11)	-15	-15	-21	-14	dB
输出回损(S22)	-16	-15	-14	-11	dB
输出功率 1dB 增益压缩点 (P1dB)	21	21	21	20	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	32	32	31	30	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	3500	3750	4000	4500	MHz
插入损耗(S21)	-23	-24	-23	-23	dB
输入回损(S11)	-2	-2	-3	-5	dB
输出回损(S22)	-9	-7	-7	-10	dB

**电气参数 (VDD=5V、108MHz-174MHz)**

低噪放模式测试条件: VDD = +5V, Iq=70mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值			单位
频率	108	136	174	MHz
小信号增益 (Gain)	23.6	24	23.8	dB
输入回损(S11)	-10.9	-9.7	-9.7	dB
输出回损(S22)	-9.5	-19.5	-13.6	dB
反向隔离(S12)	-30.6	-30	-30.3	dB
噪声系数 (NF)	0.6	0.68	0.58	dB
输出功率 1dB 增益压缩点 (P1dB)	16.6	17.2	15.8	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	34.1	35.0	36.4	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +5V, Iq=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值			单位
频率	108	136	174	MHz
插入损耗(S21)	-1.6	-1.2	-1.3	dB
输入回损(S11)	-9.6	-16.1	-13	dB
输出回损(S22)	-10.7	-26	-13.1	dB

关断模式测试条件: VDD = +5V, Iq=7mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值			单位
频率	108	136	174	MHz
插入损耗(S21)	-26.1	-25.7	-25.3	dB
输入回损(S11)	-0.6	-0.6	-0.7	dB
输出回损(S22)	-5.1	-5.8	-7	dB

**电气参数 (VDD=5V、200MHz-2500MHz)**

低噪放模式测试条件: VDD = +5V, Iq=68mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	500	1000	1500	2500	MHz
小信号增益 (Gain)	24	22	20	18	dB
输入回损(S11)	-10	-9	-13	-11	dB
输出回损(S22)	-12	-8	-7	-10	dB
反向隔离(S12)	-30	-30	-33	-38	dB
噪声系数 (NF)	0.7	0.6	0.8	1.3	dB
输出功率 1dB 增益压缩点 (P1dB)	17	18	19	18	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	34	33	34	34	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +5V, Iq=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	500	1000	1500	2500	MHz
插入损耗(S21)	-2	-1	-2	-2	dB
输入回损(S11)	-7	-15	-13	-9	dB
输出回损(S22)	-6	-13	-10	-10	dB
输出功率 1dB 增益压缩点 (P1dB)	23	23	22	22	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	39	40	39	38	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

关断模式测试条件: VDD = +5V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	500	1000	1500	2500	MHz
插入损耗(S21)	-23	-25	-22	-23	dB
输入回损(S11)	-0.7	-0.9	-1.8	-2.5	dB
输出回损(S22)	-8	-3	-5	-5	dB

**电气参数 (VDD=5V、2500MHz-3500MHz)**

低噪放模式测试条件: VDD = +5V, Iq=71mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	2500	2750	3000	3500	MHz
小信号增益 (Gain)	17	18	17	17	dB
输入回损(S11)	-11	-16	-28	-13	dB
输出回损(S22)	-8	-11	-16	-10	dB
反向隔离(S12)	-36	-36	-42	-41	dB
噪声系数 (NF)	1.1	1.2	1.3	1.7	dB
输出功率 1dB 增益压缩点 (P1dB)	19	19	18	17	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	32	32	31	30	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +5V, Iq=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	2500	2750	3000	3500	MHz
插入损耗(S21)	-2	-2	-2	-2	dB
输入回损(S11)	-13	-13	-12	-15	dB
输出回损(S22)	-13	-13	-17	-18	dB
输出功率 1dB 增益压缩点 (P1dB)	22	22	22	21	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	39	38	36	30	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

关断模式测试条件: VDD = +5V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	2500	2750	3000	3500	MHz
插入损耗(S21)	-23	-23	-22	-22	dB
输入回损(S11)	-1	-2	-3	-3	dB
输出回损(S22)	-7	-10	-9	-7	dB

**电气参数 (VDD=5V、3500MHz-4500MHz)**

低噪放模式测试条件: VDD = +5V, Iq=75mA, LNA ON, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	3500	3750	4000	4500	MHz
小信号增益 (Gain)	17	17	16	14	dB
输入回损(S11)	-14	-15	-16	-17	dB
输出回损(S22)	-15	-9	-8	-9	dB
反向隔离(S12)	-33	-35	-33	-34	dB
噪声系数 (NF)	1.5	1.5	1.7	2.2	dB
输出功率 1dB 增益压缩点 (P1dB)	18	17	16	15	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	32	31	31	30	dBm

注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

旁路模式测试条件: VDD = +5V, Iq=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	3500	3750	4000	4500	MHz
插入损耗(S21)	-2	-2	-2	-3	dB
输入回损(S11)	-15	-15	-20	-15	dB
输出回损(S22)	-16	-16	-14	-11	dB
输出功率 1dB 增益压缩点 (P1dB)	21	21	21	20	dBm
输出三阶交调 ⁽¹⁾ (OIP3)	30	30	33	31	dBm

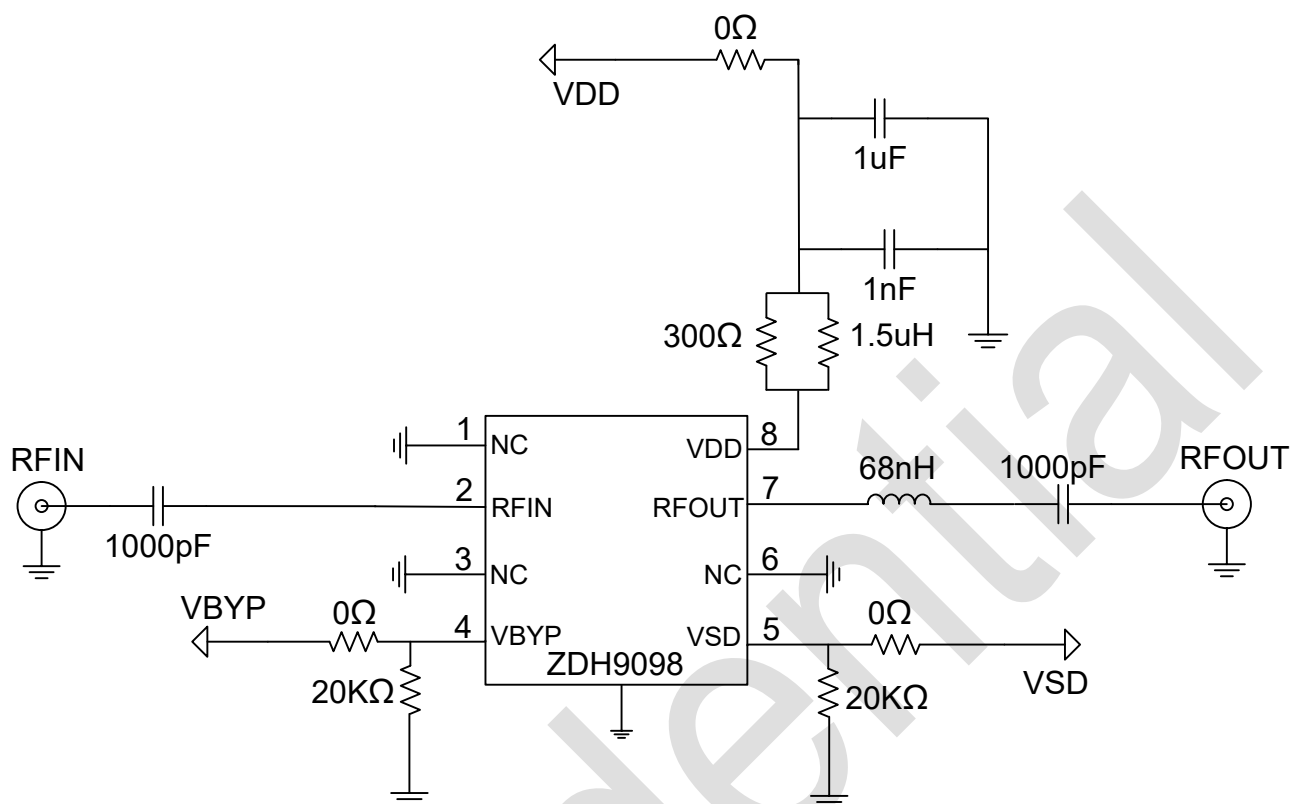
注: (1) 两个 tone 间隔 1MHz, 每个 tone 输出功率为 0dBm。

关断模式测试条件: VDD = +5V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。

参数	典型值				单位
频率	3500	3750	4000	4500	MHz
插入损耗(S21)	-23	-24	-23	-23	dB
输入回损(S11)	-2	-2	-2	-5	dB
输出回损(S22)	-9	-7	-7	-10	dB

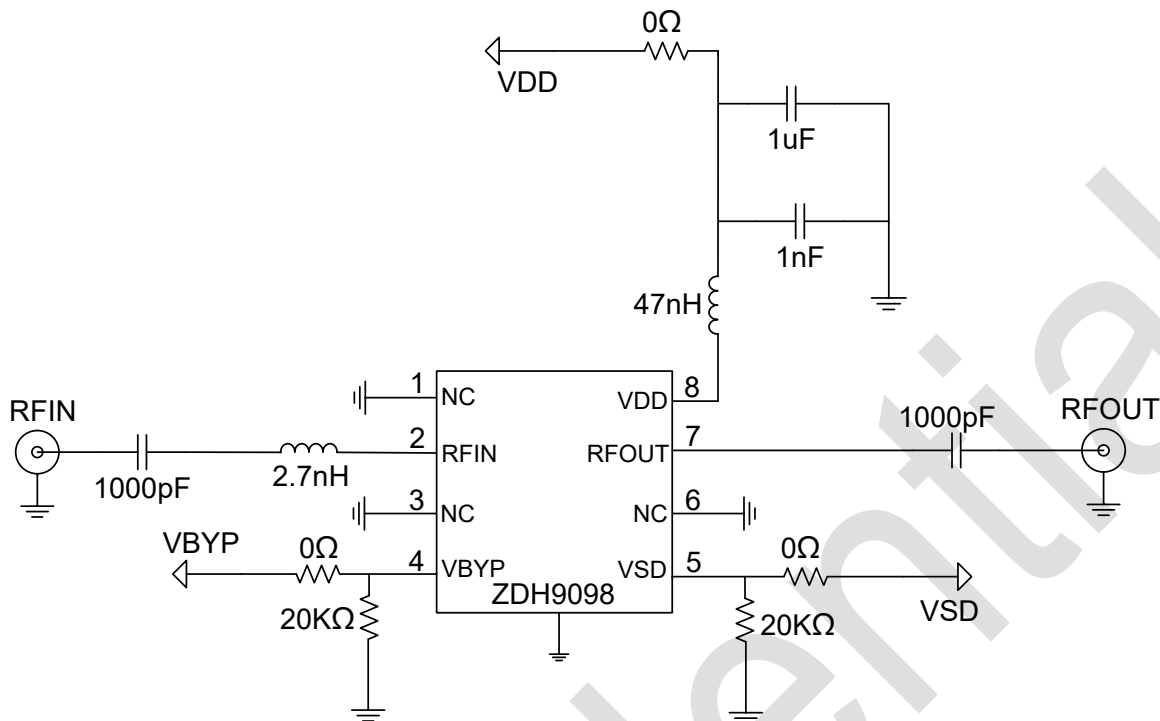


应用电路图 (108MHz~174MHz)

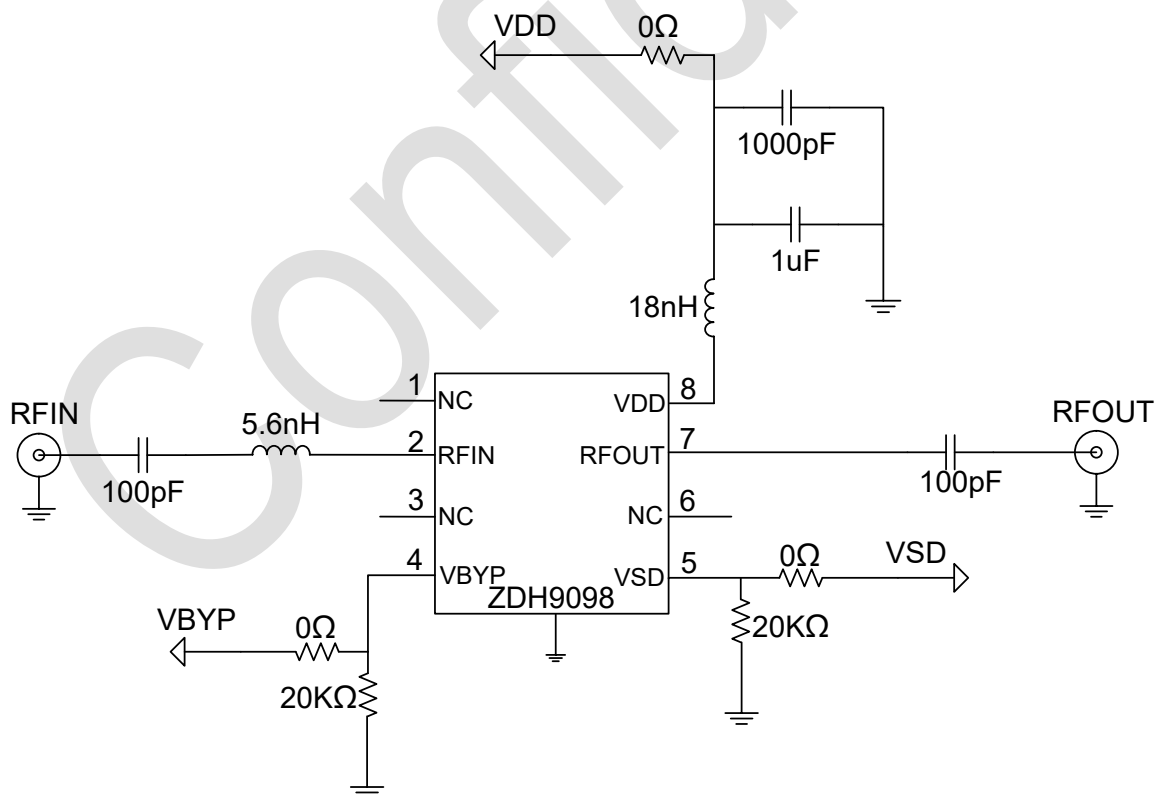




应用电路图（200MHz~2500MHz）

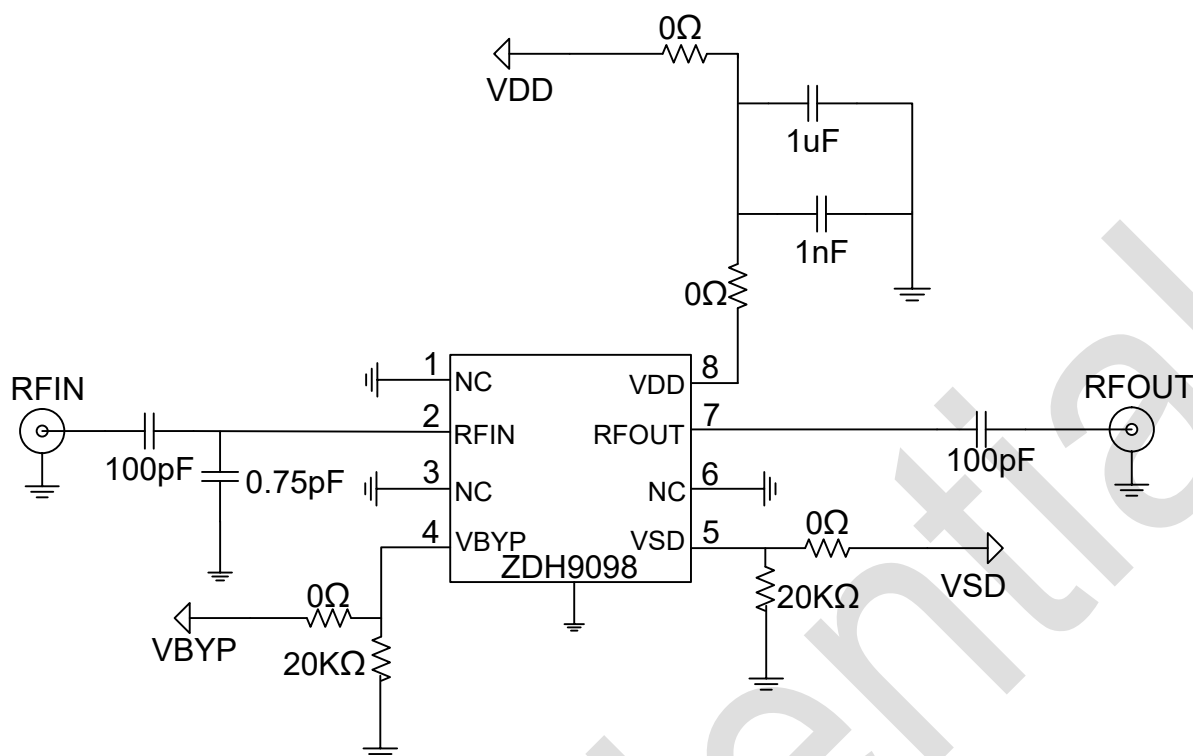


应用电路图（2500MHz~3500MHz）



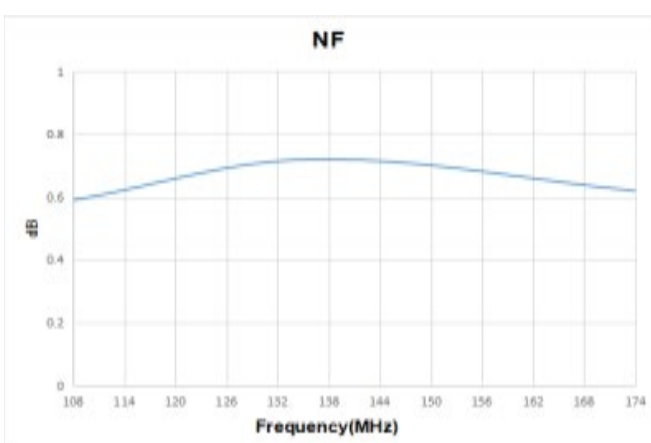
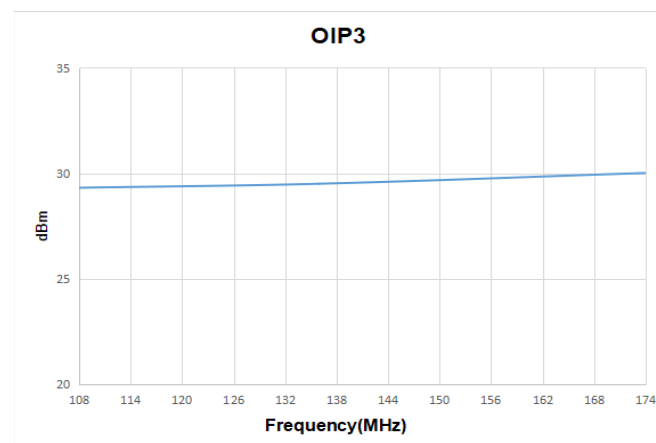
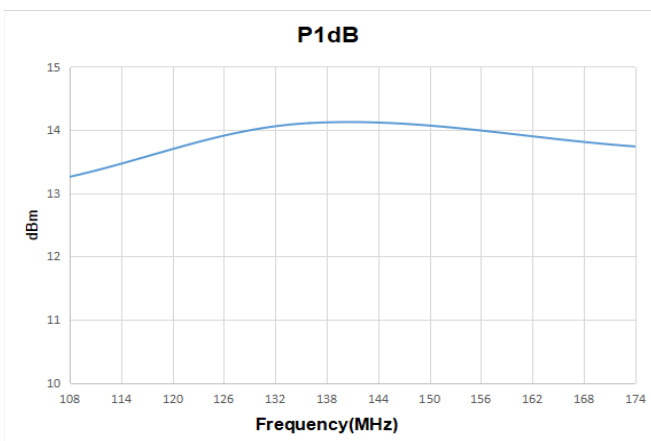
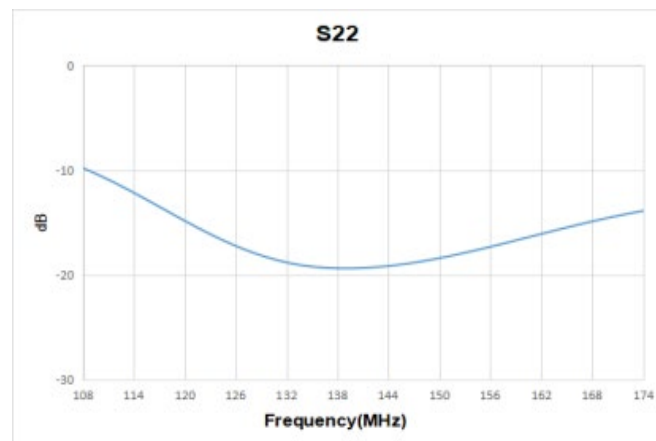
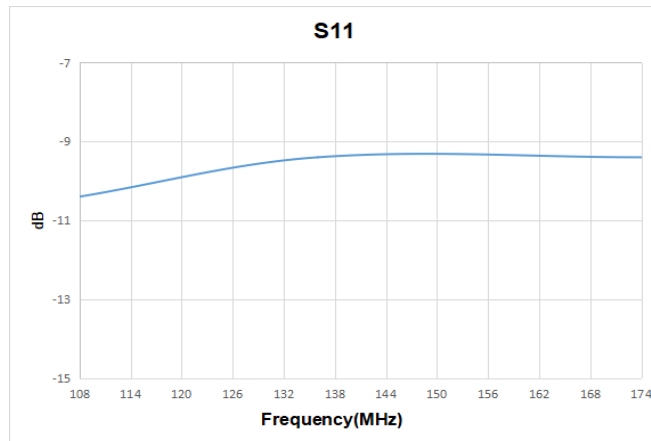
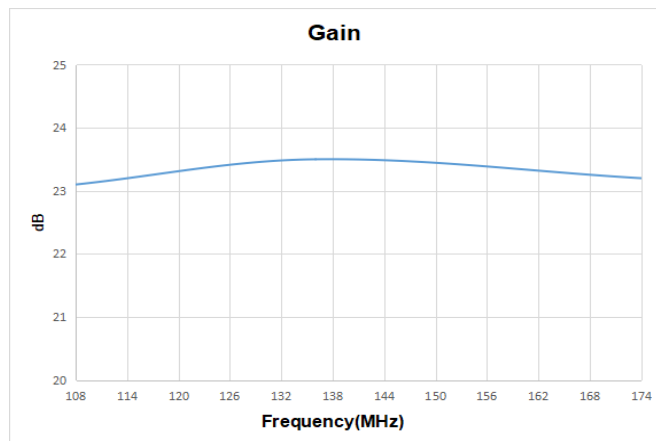


应用电路图（3500MHz~4500MHz）



典型性能曲线(VDD=+3.3V、108MHz-174MHz)

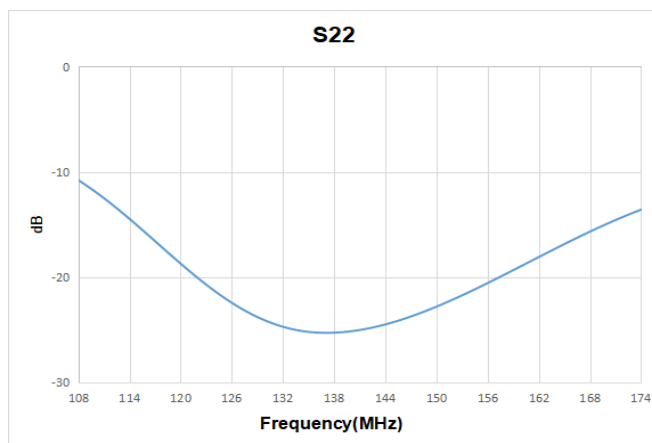
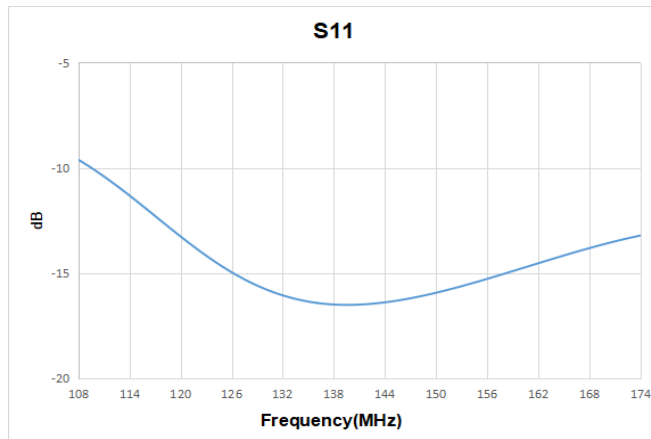
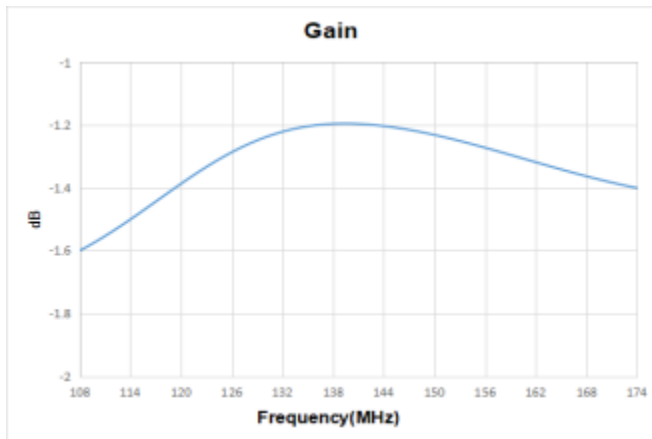
低噪放模式测试条件: VDD = +3.3V, Iq=48mA, LNA ON, Bypass OFF, 50Ω 测试系统。





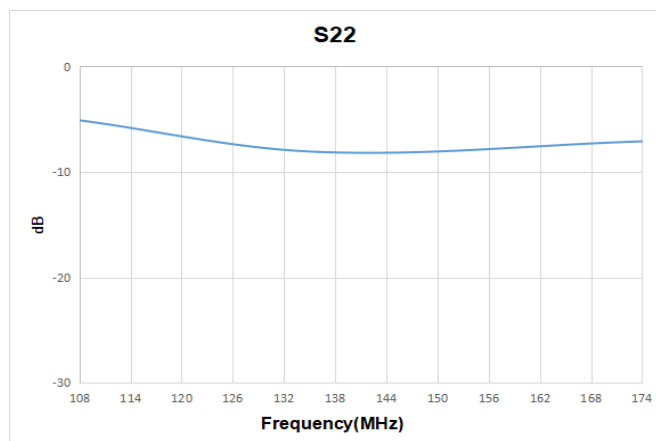
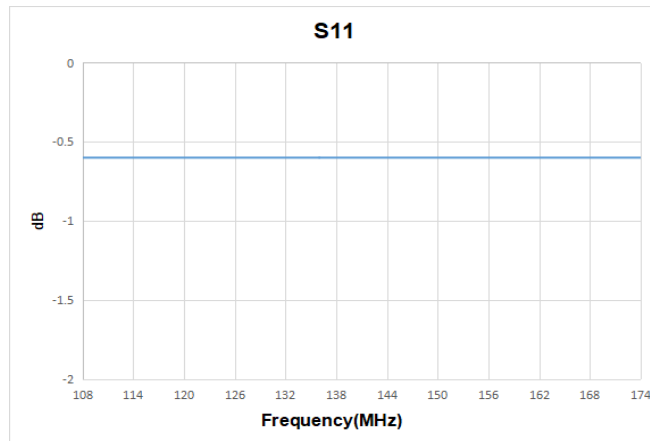
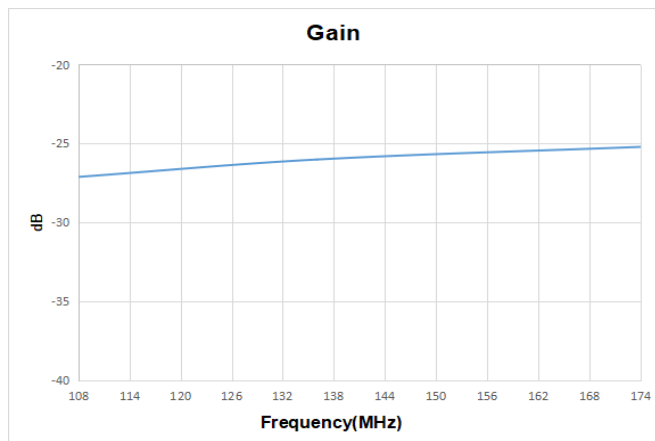
典型性能曲线(VDD=+3.3V、108MHz-174MHz)

旁路模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。



典型性能曲线(VDD=+3.3V、108MHz-174MHz)

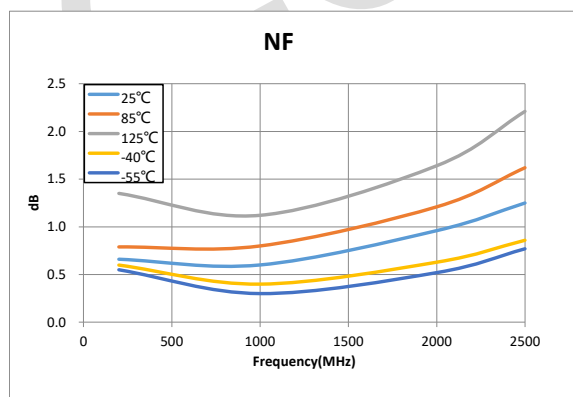
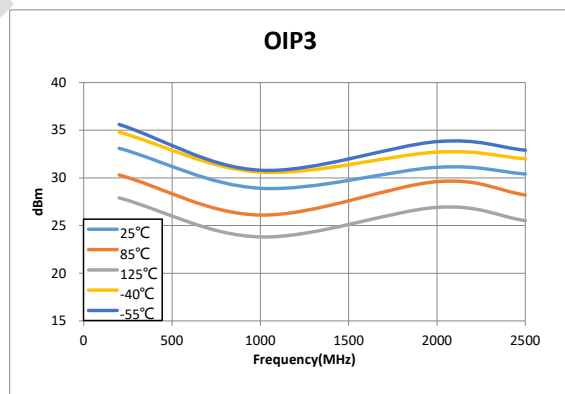
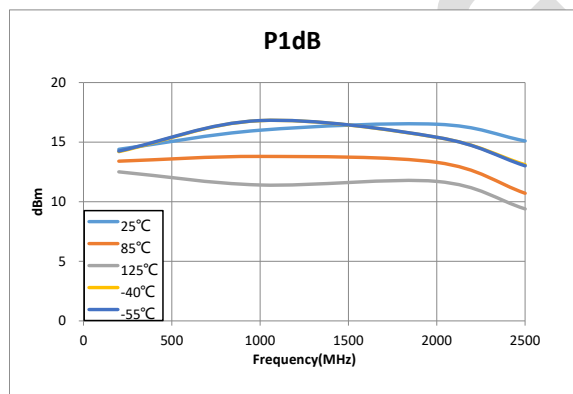
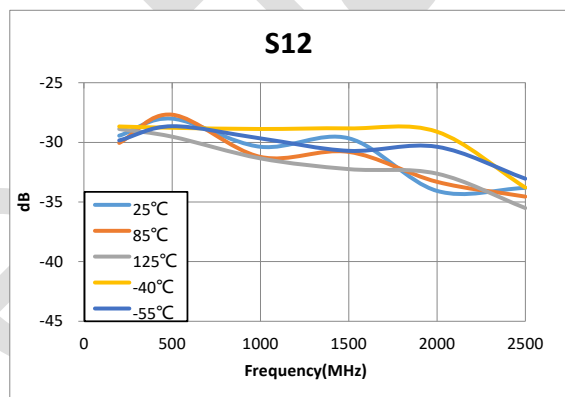
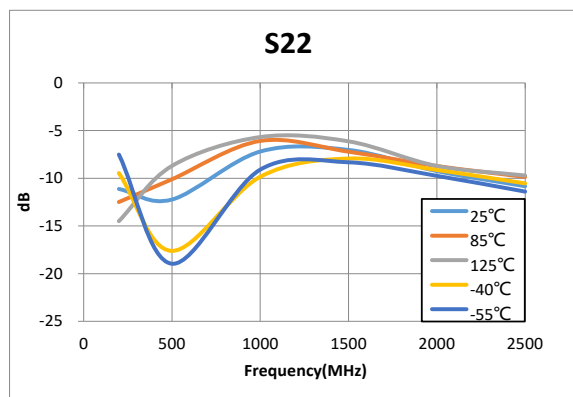
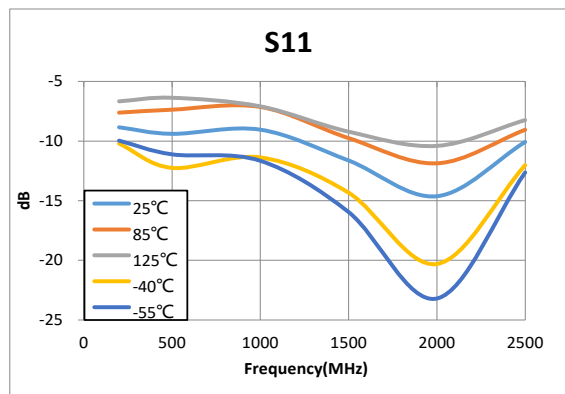
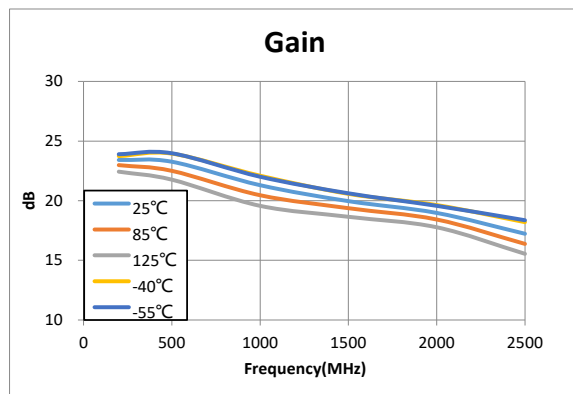
关断模式测试条件: VDD = +3.3V, Iq=4mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。





典型性能曲线(VDD=+3.3V、200MHz-2500MHz)

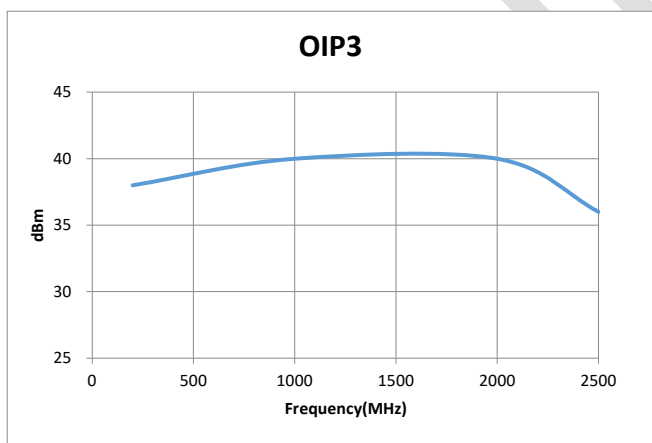
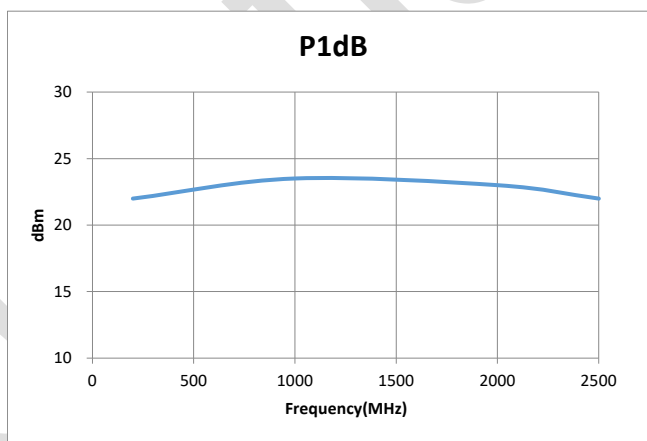
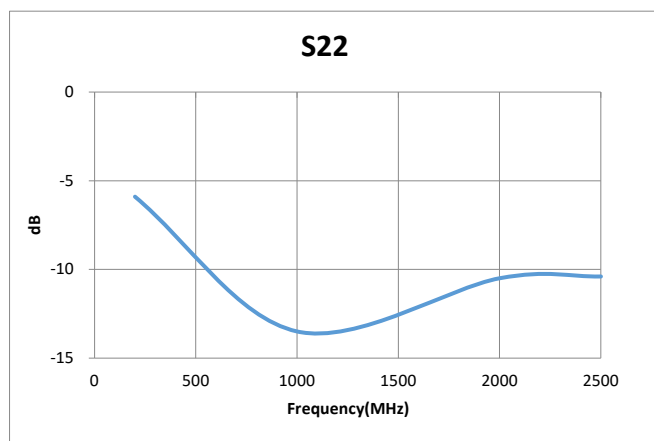
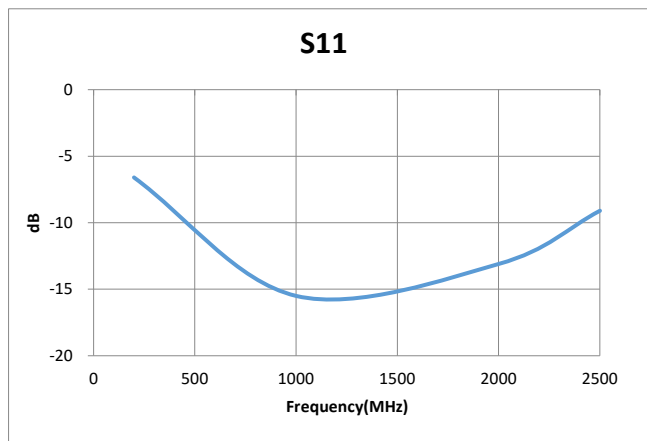
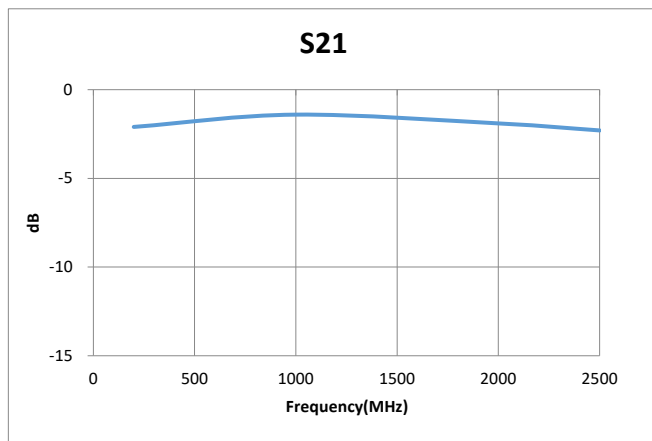
低噪放模式测试条件: VDD = +3.3V, Iq=45mA, LNA ON, Bypass OFF, 50Ω 测试系统。





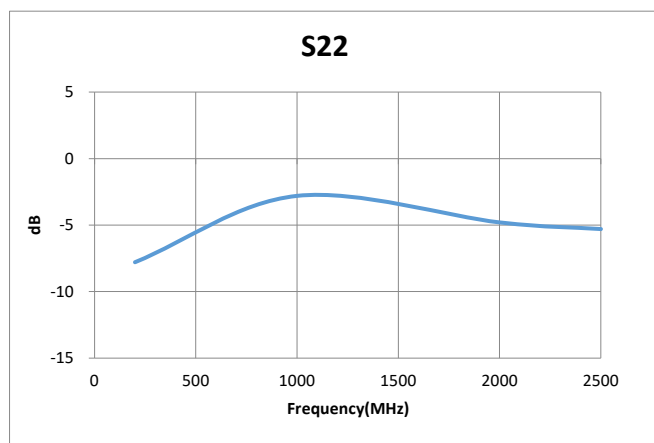
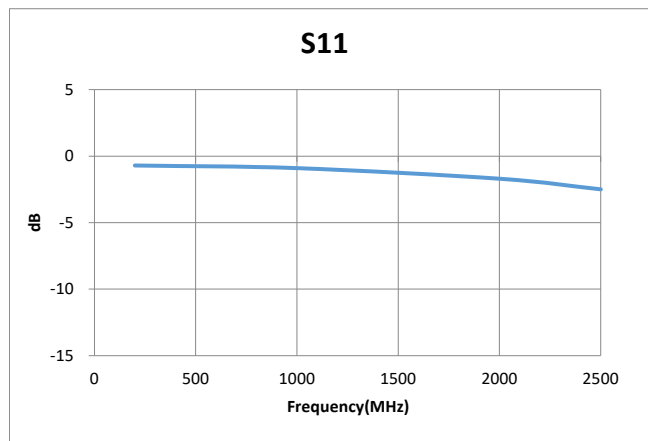
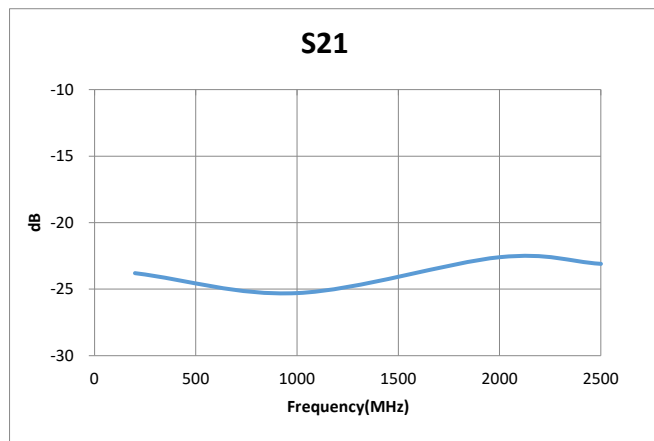
典型性能曲线(VDD=+3.3V、200MHz-2500MHz)

旁路模式测试条件: VDD = +3.3V, Iq=6mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。



**典型性能曲线(VDD=+3.3V、200MHz-2500MHz)**

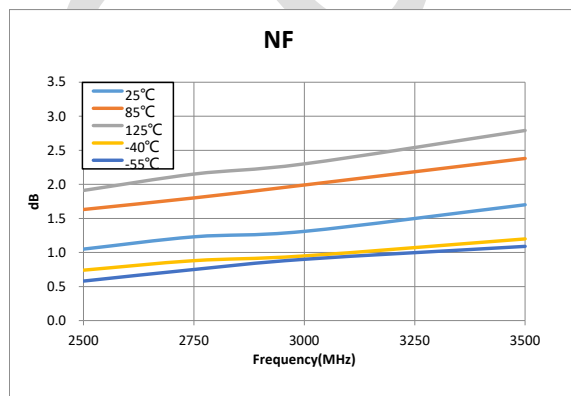
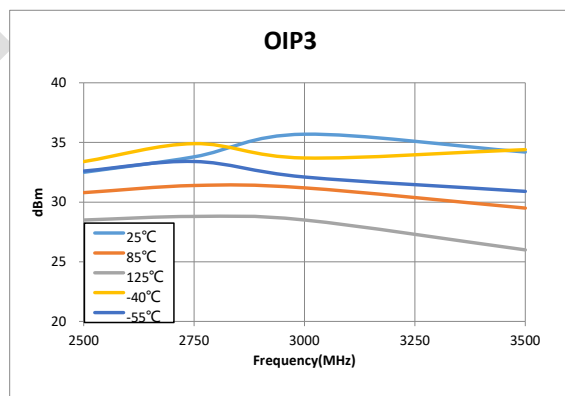
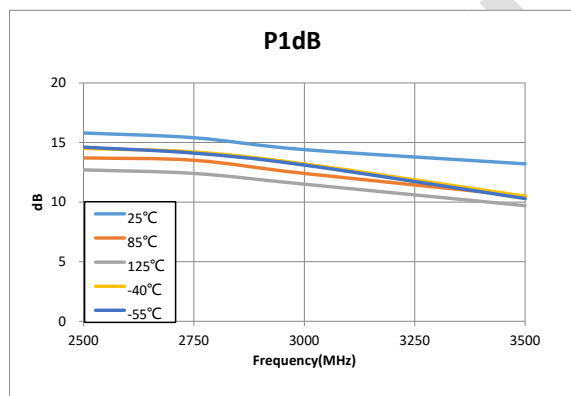
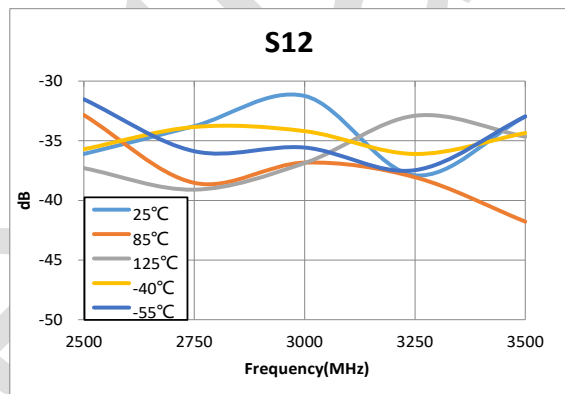
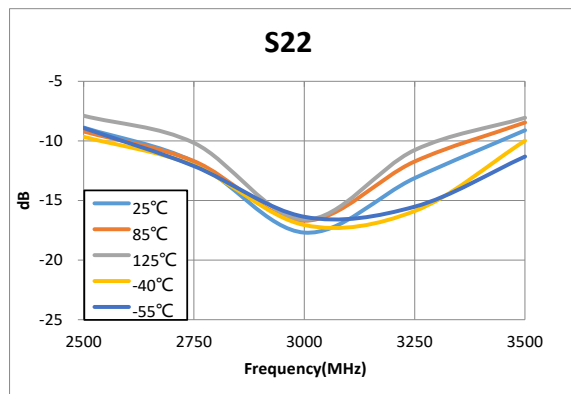
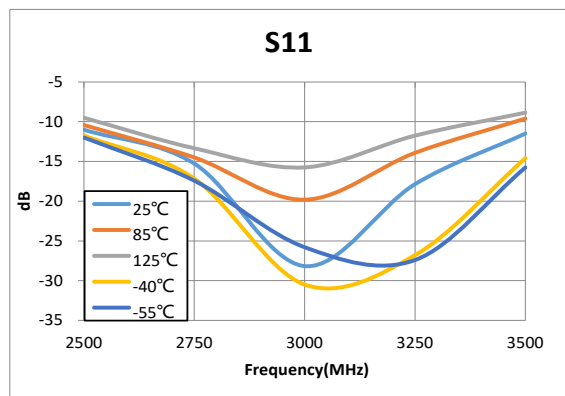
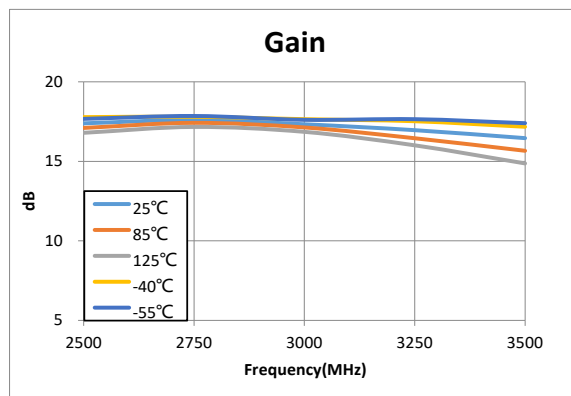
关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。





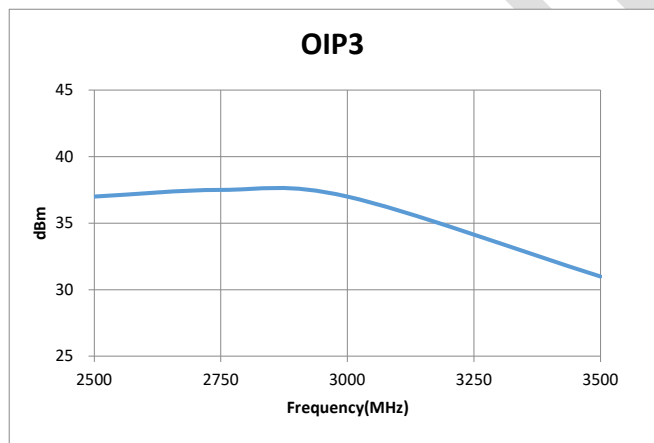
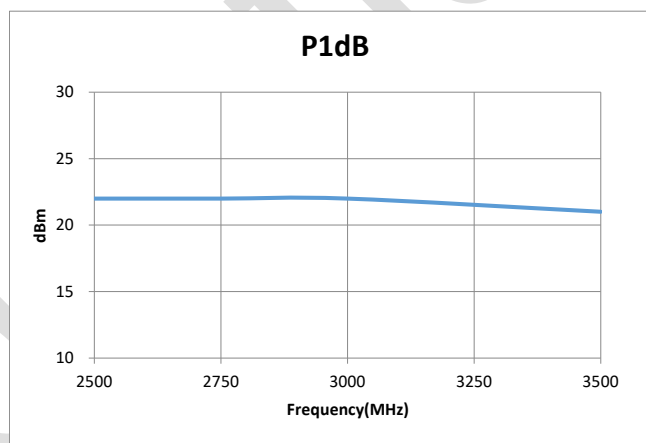
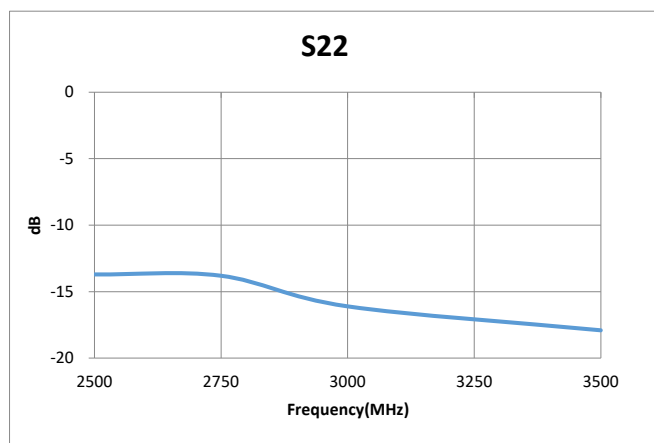
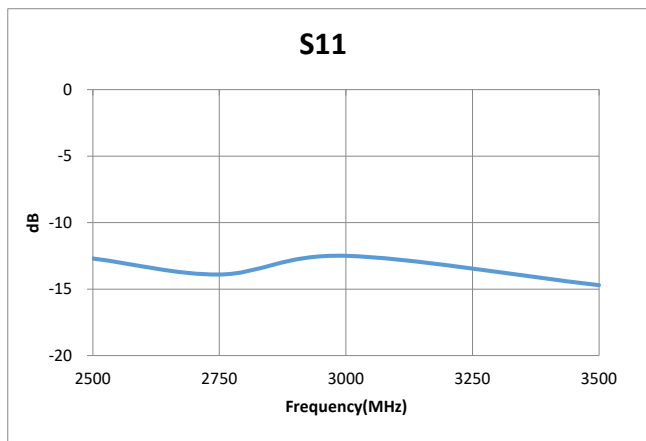
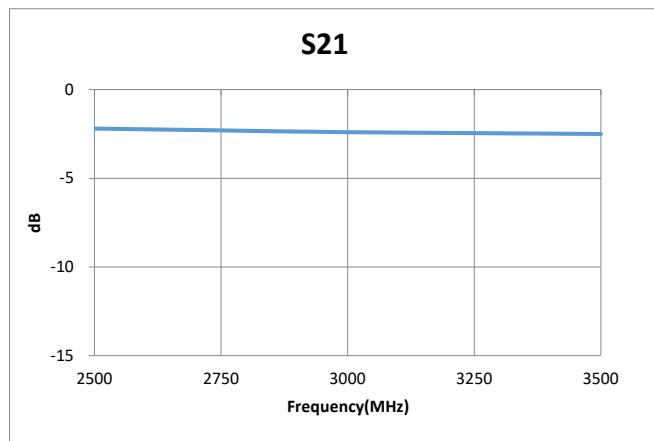
典型性能曲线(VDD=+3.3V、2500MHz-3500MHz)

低噪放模式测试条件: VDD = +3.3V, Iq=47mA, LNA ON, Bypass OFF, 50Ω 测试系统。



**典型性能曲线(VDD=+3.3V、2500MHz-3500MHz)**

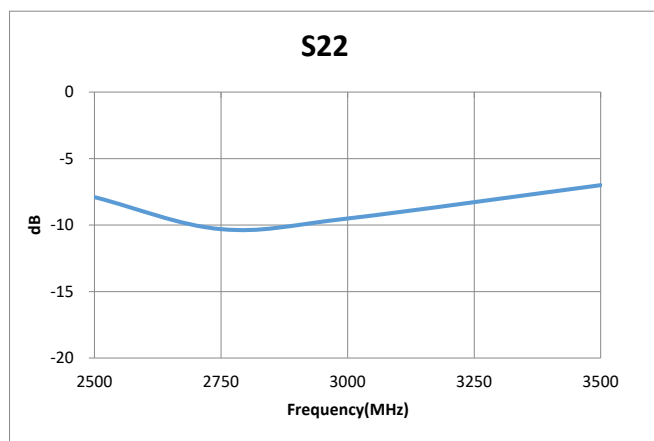
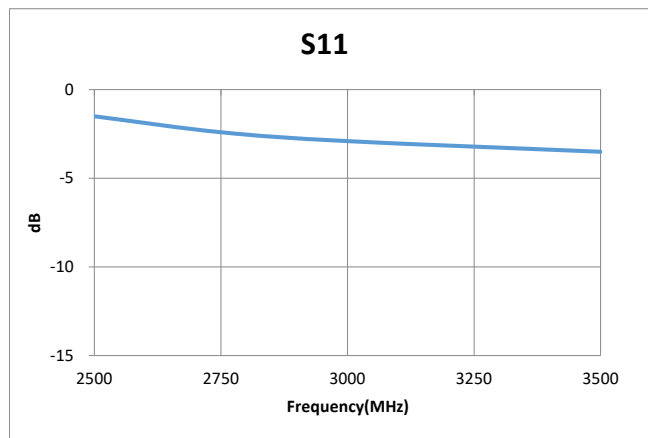
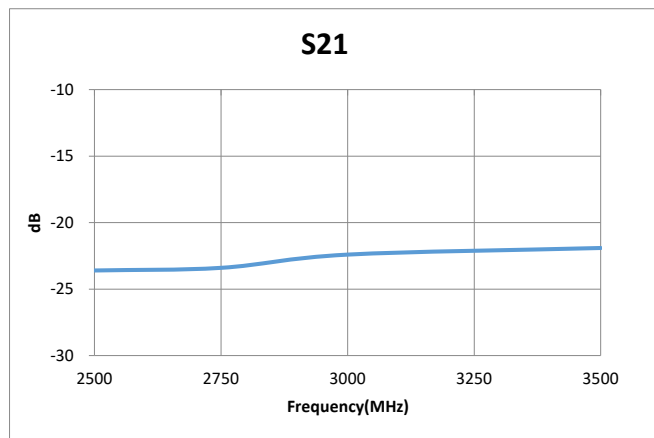
旁路模式测试条件: VDD = +3.3V, Iq=6mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。





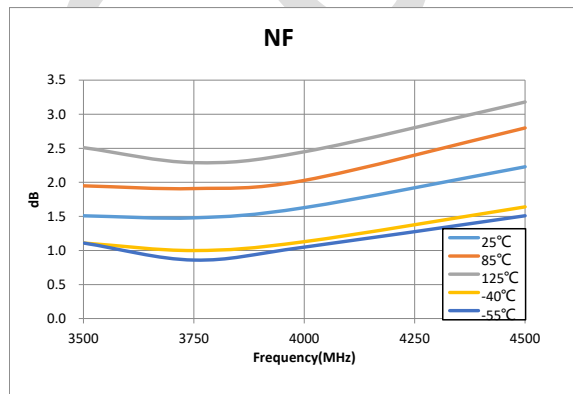
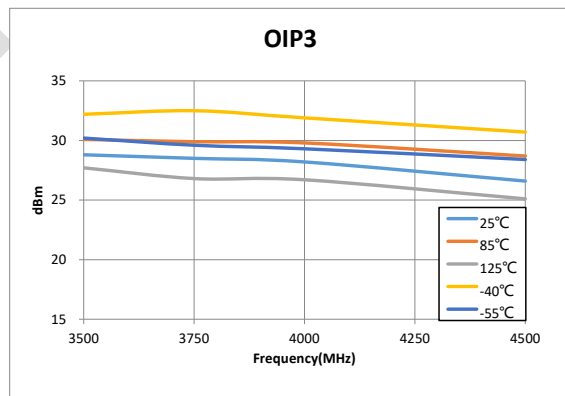
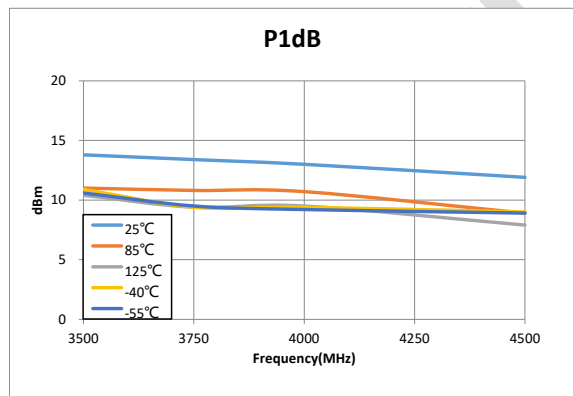
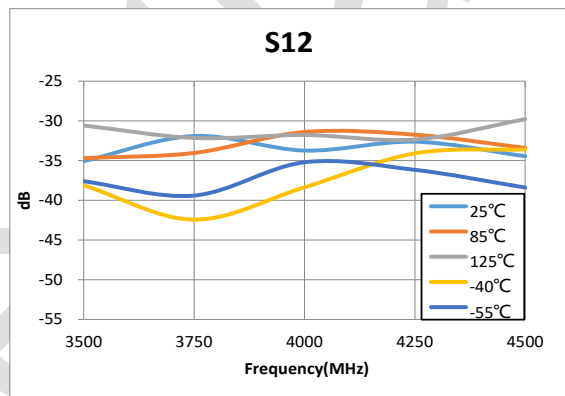
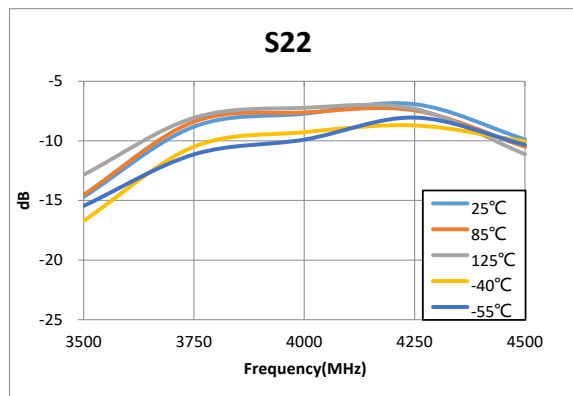
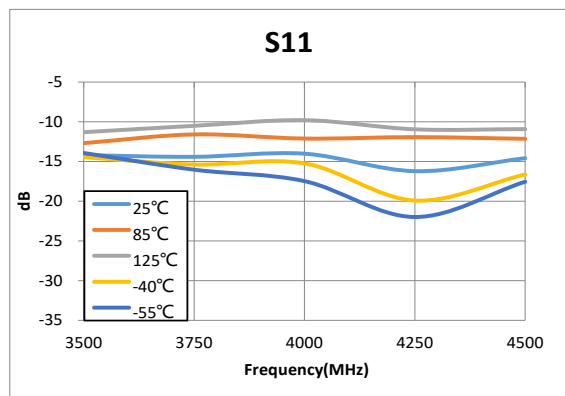
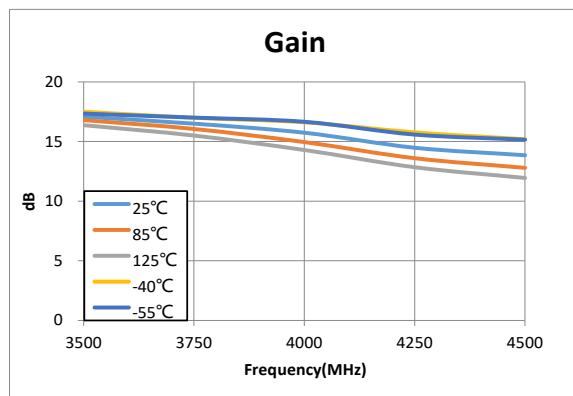
典型性能曲线(VDD=+3.3V、2500MHz-3500MHz)

关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。



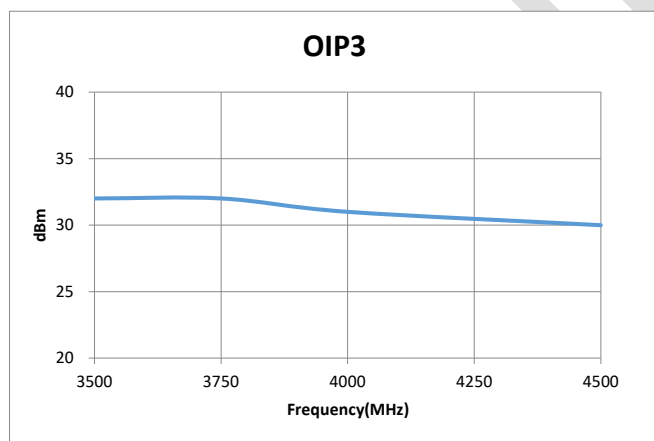
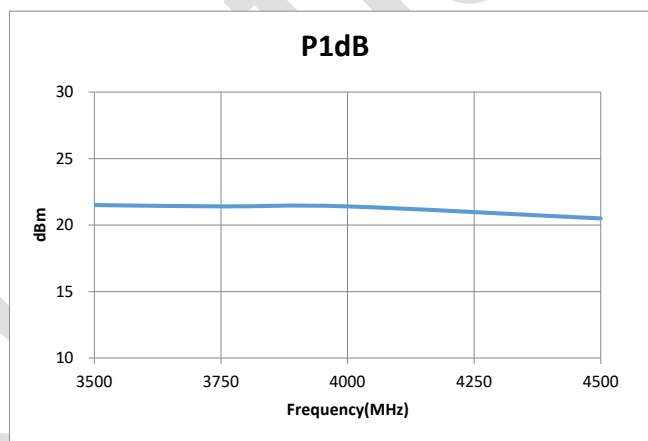
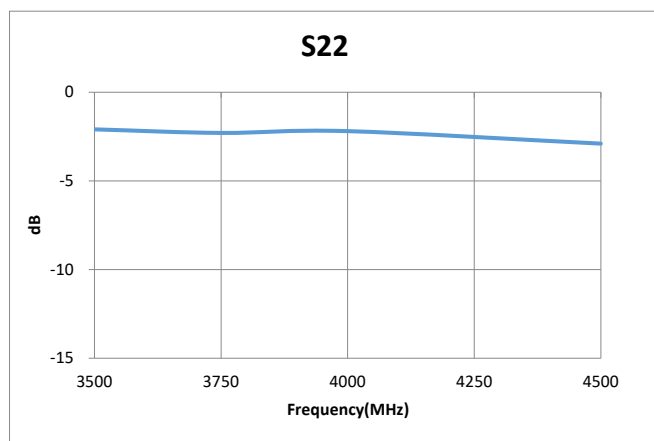
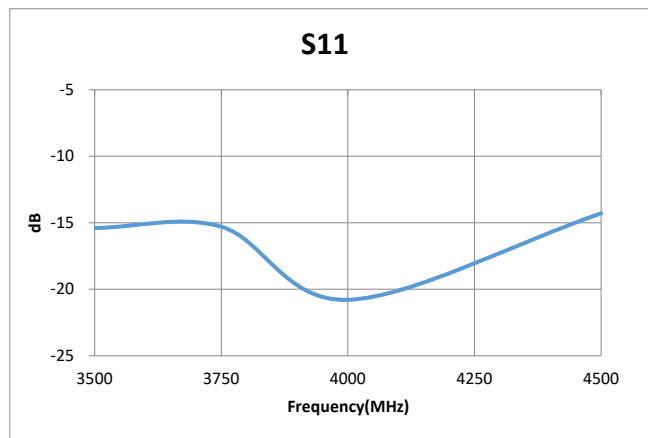
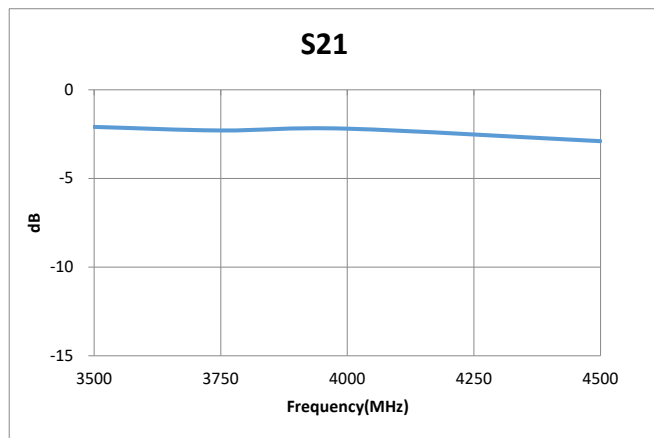


典型性能曲线(VDD=+3.3V、3500MHz-4500MHz)

低噪放模式测试条件: VDD = +3.3V, I_q=51mA, LNA ON, Bypass OFF, 50Ω 测试系统。

典型性能曲线(VDD=+3.3V、3500MHz-4500MHz)

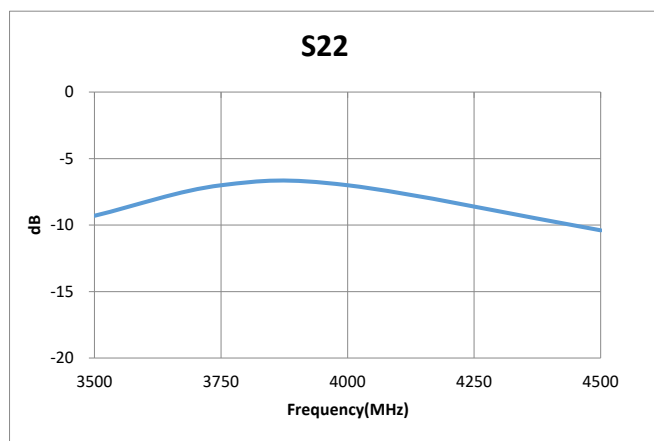
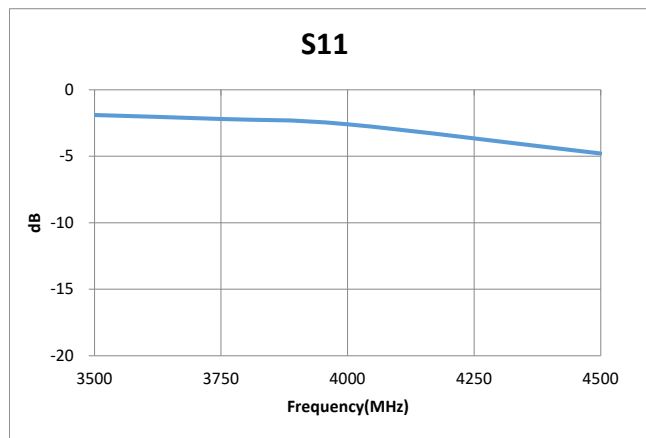
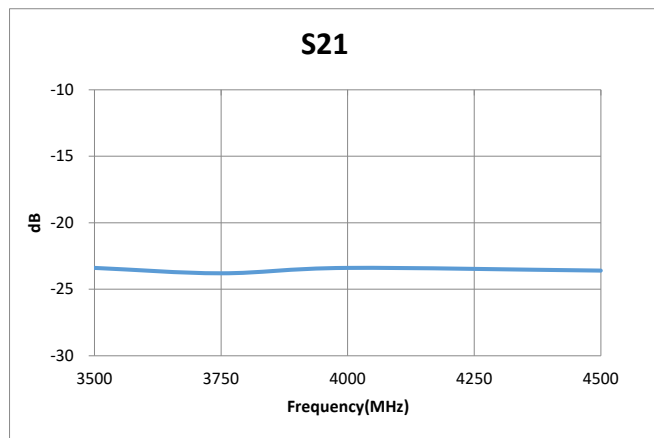
旁路模式测试条件: VDD = +3.3V, Iq=6mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。





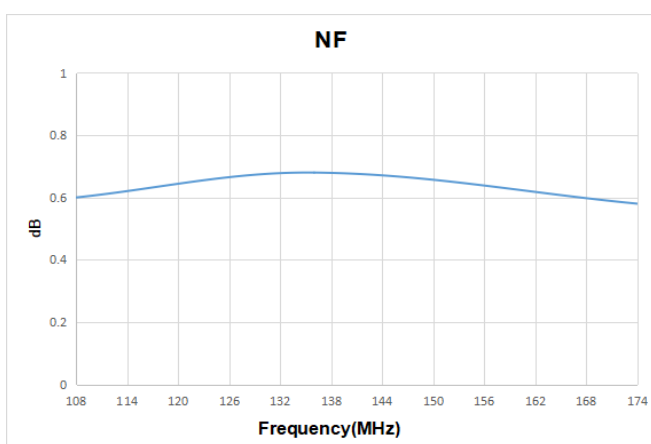
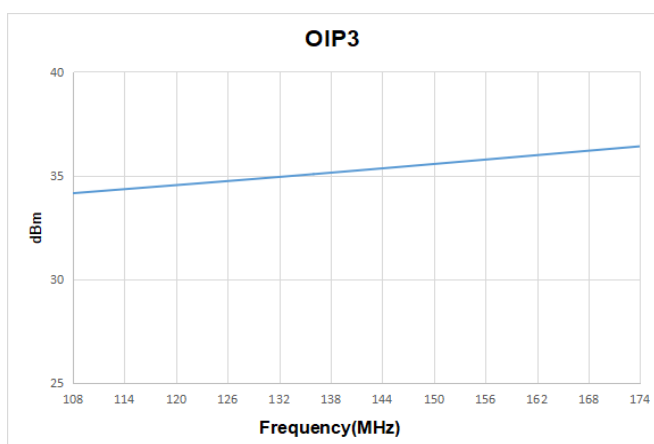
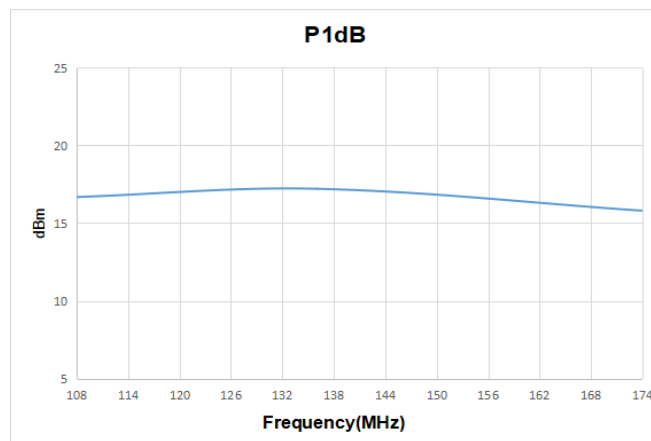
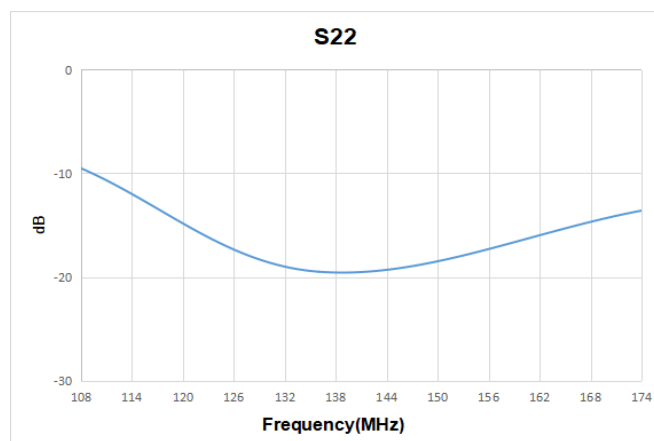
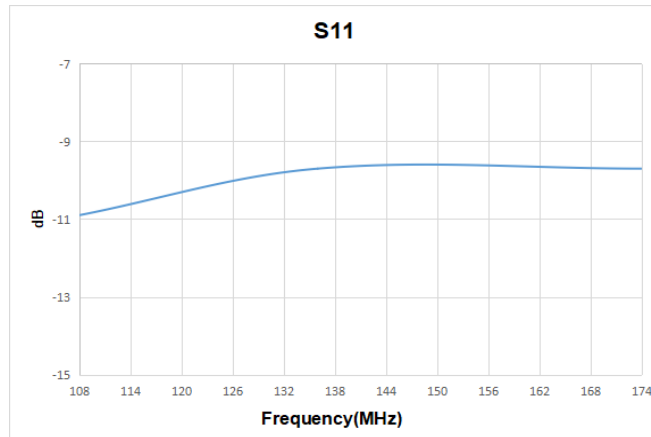
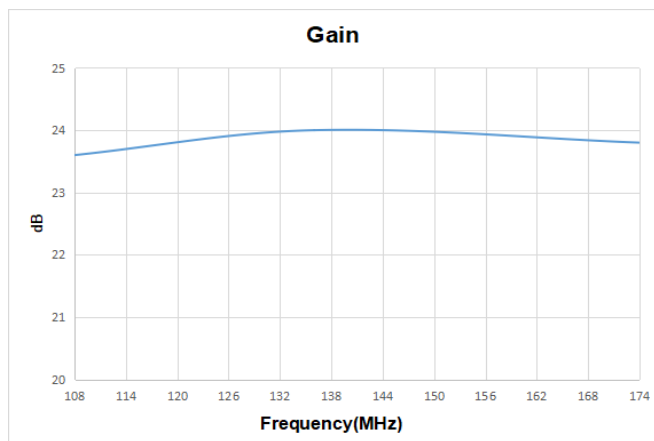
典型性能曲线(VDD=+3.3V、3500MHz-4500MHz)

关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。



典型性能曲线(VDD=+5V、108MHz-174MHz)

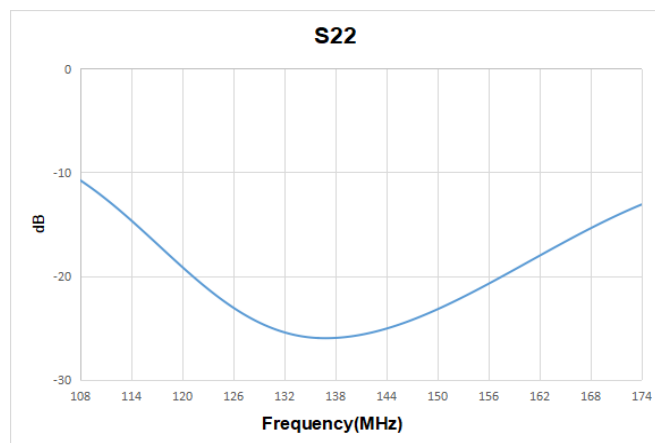
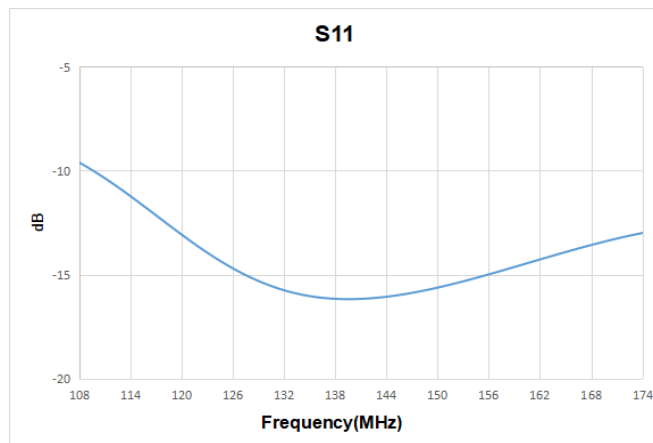
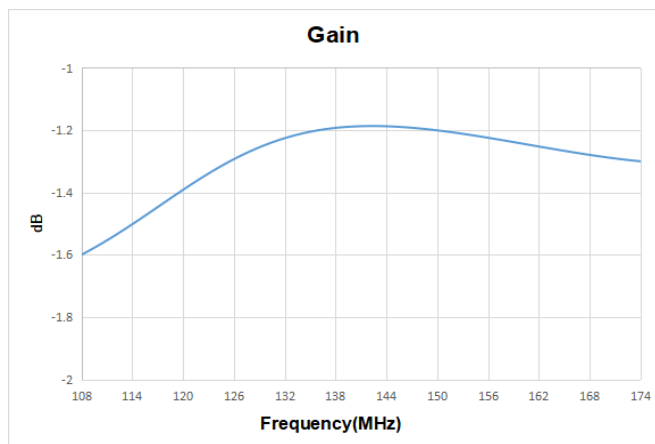
低噪声模式测试条件: VDD = +5V, Iq=70mA, LNA ON, Bypass OFF, 50Ω 测试系统。





典型性能曲线(VDD=+5V、108MHz-174MHz)

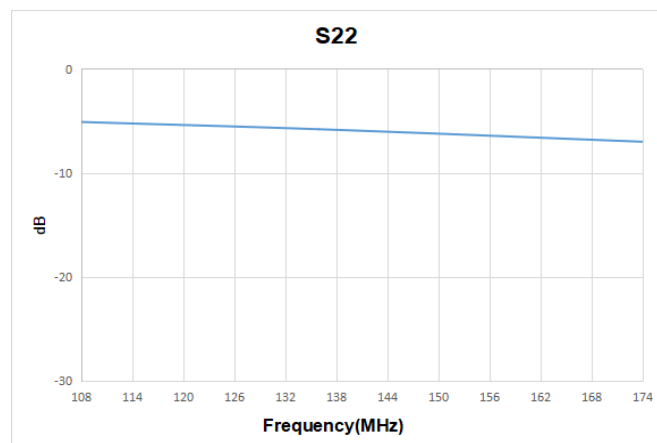
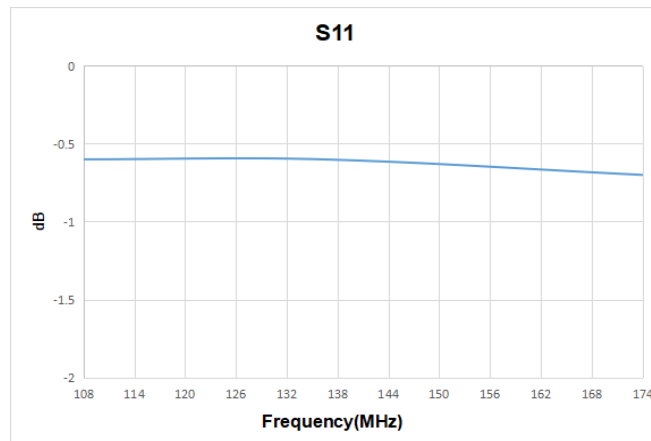
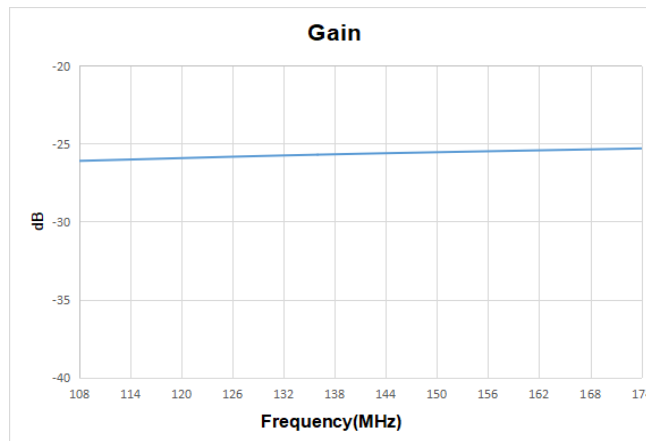
旁路模式测试条件: VDD = +5V, Iq=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。





典型性能曲线(VDD=+5V、108MHz-174MHz)

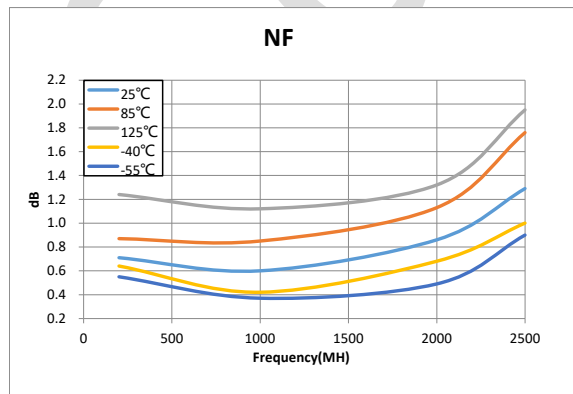
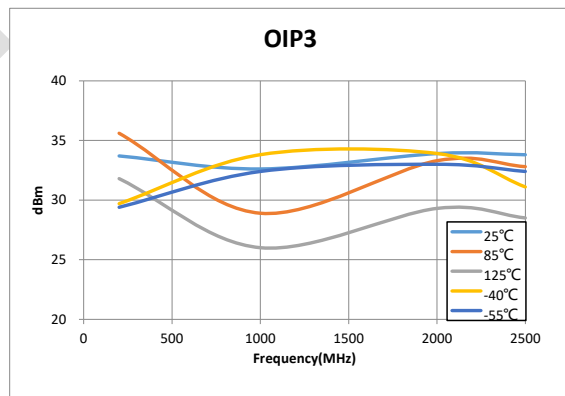
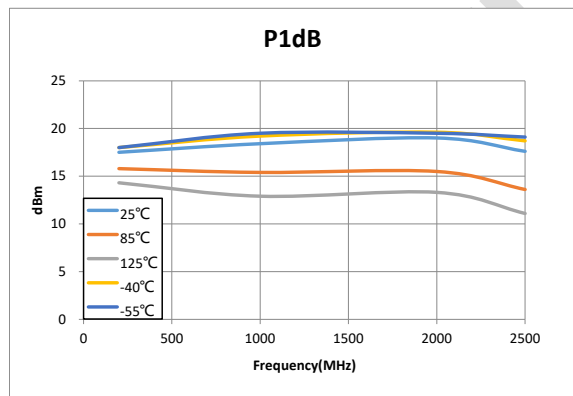
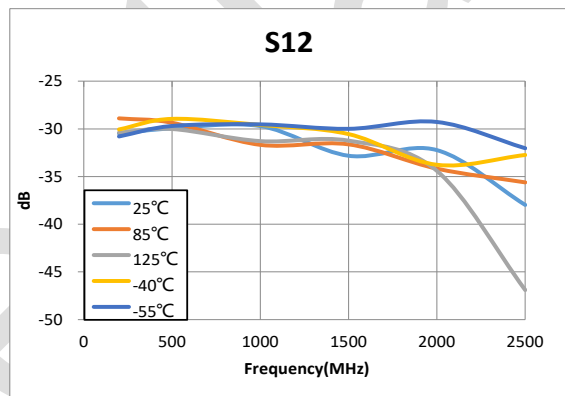
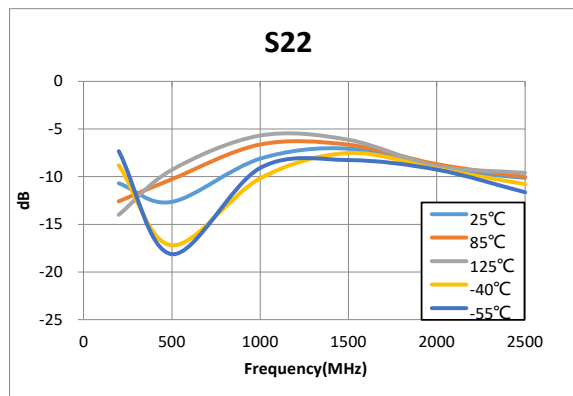
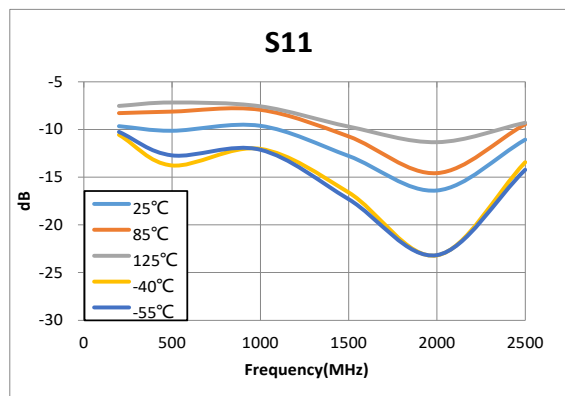
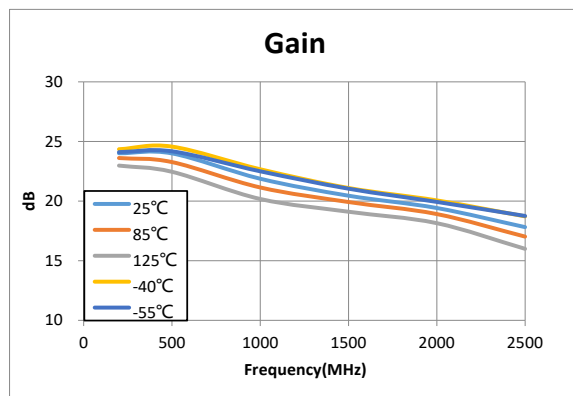
关断模式测试条件: VDD = +5V, Iq=7mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。





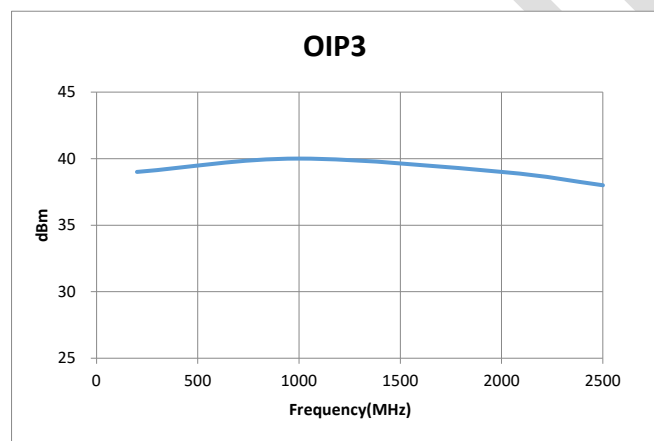
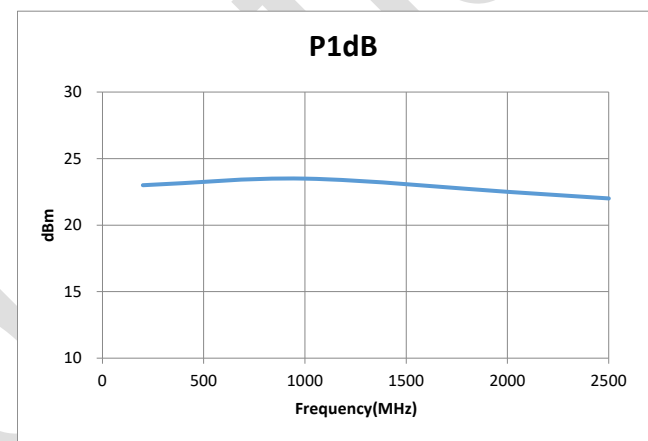
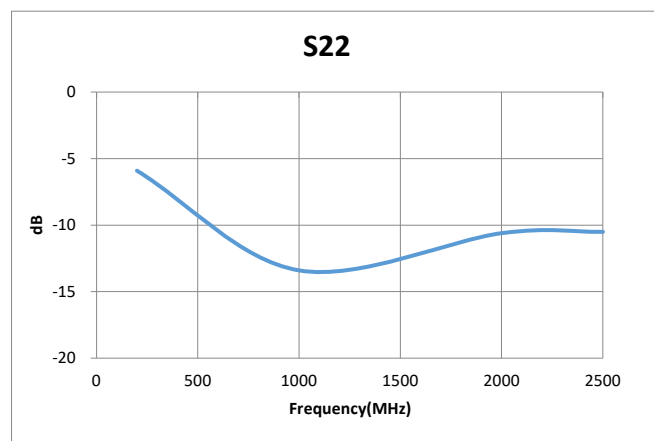
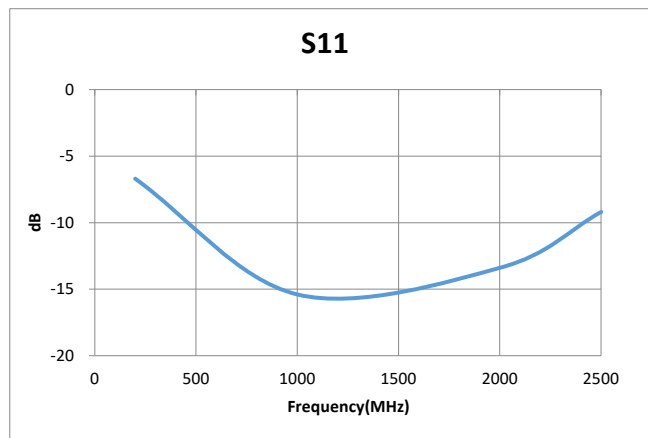
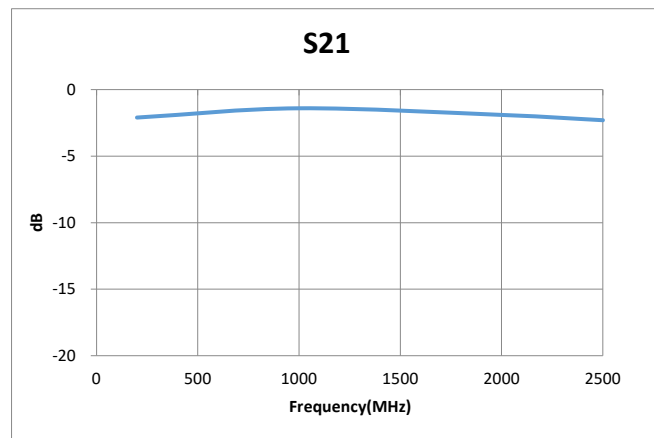
典型性能曲线(VDD=+5V、200MHz-2500MHz)

低噪放模式测试条件: VDD = +5V, Iq=68mA, LNA ON, Bypass OFF, 50Ω 测试系统。



**典型性能曲线(VDD=+5V、200MHz-2500MHz)**

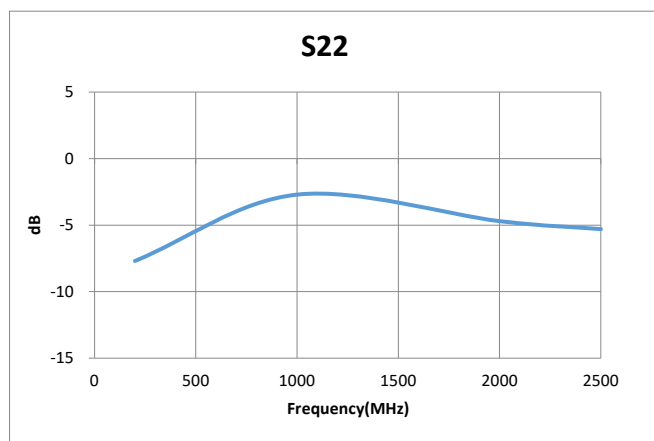
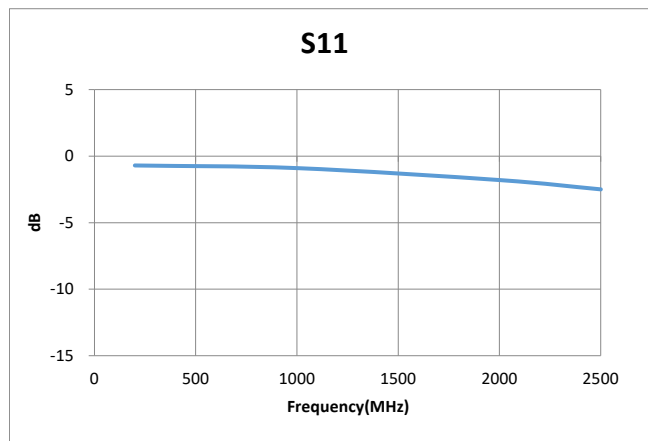
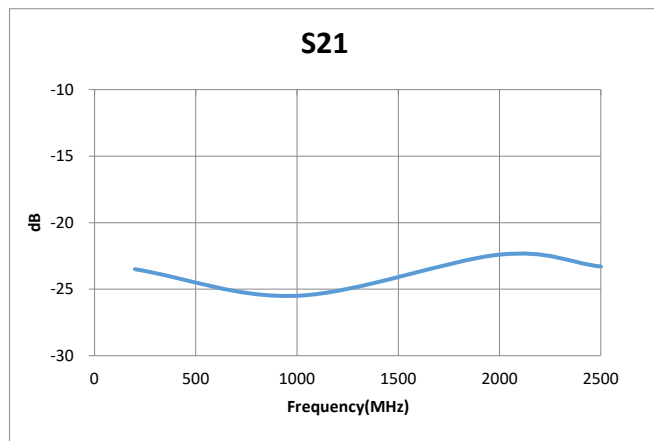
旁路模式测试条件: VDD = +5V, I_q=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。





典型性能曲线(VDD=+5V、200MHz-2500MHz)

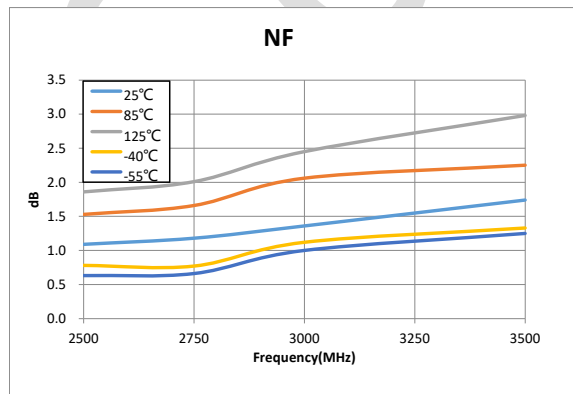
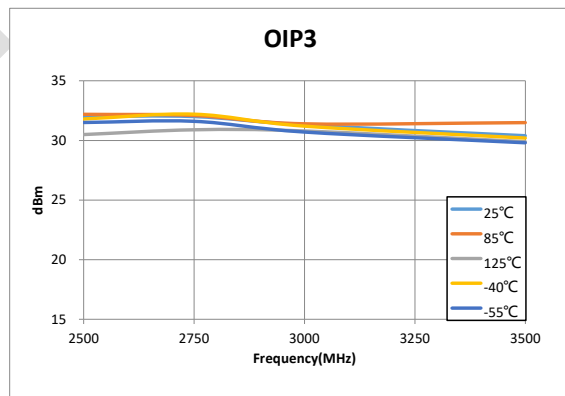
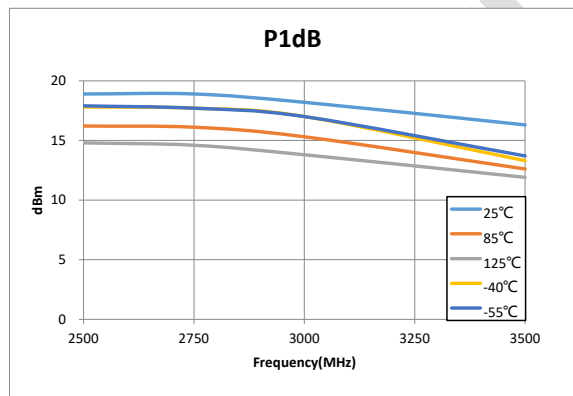
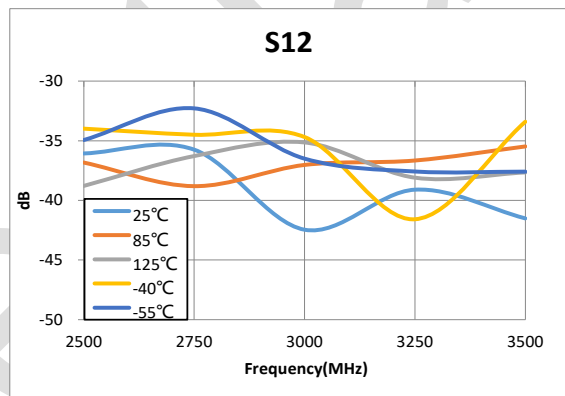
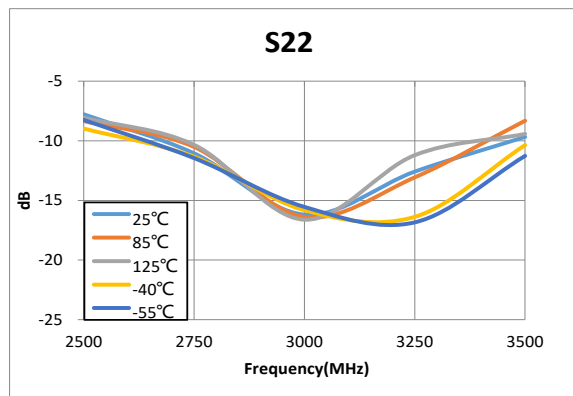
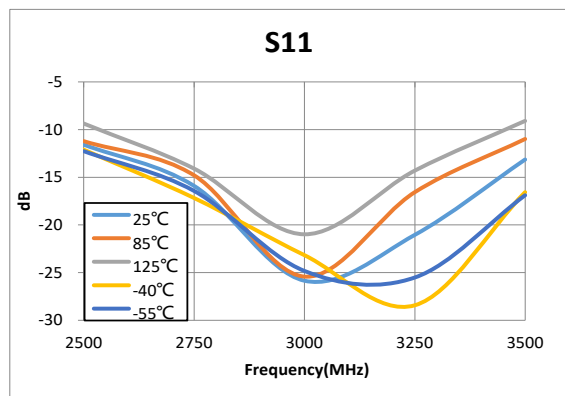
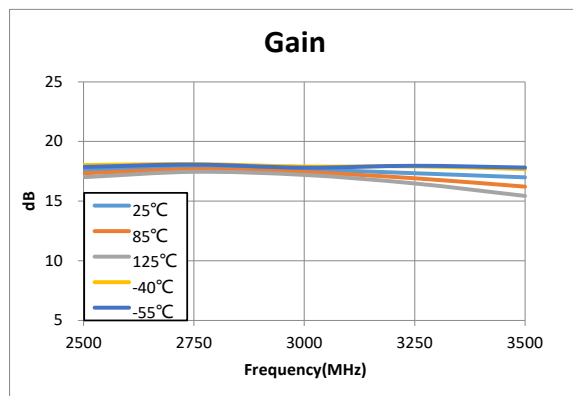
关断模式测试条件: VDD = +5V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。





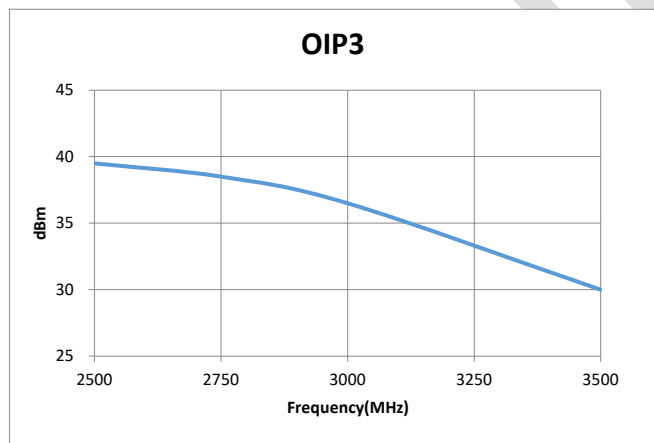
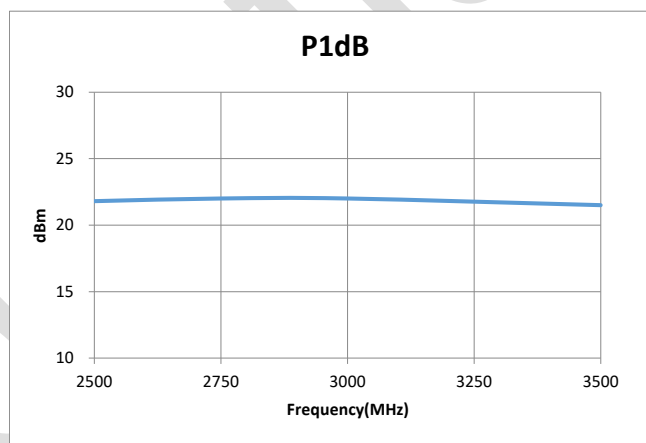
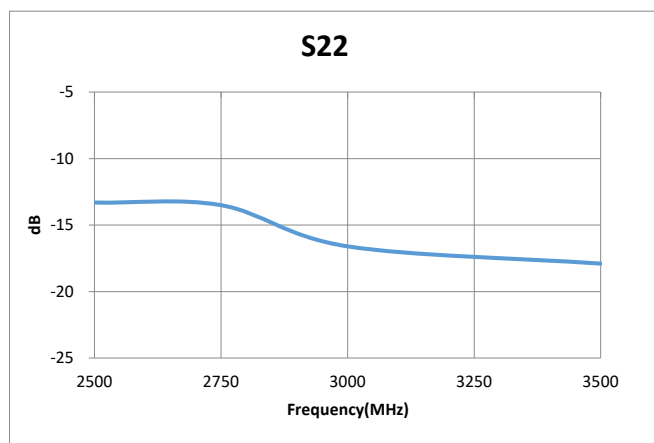
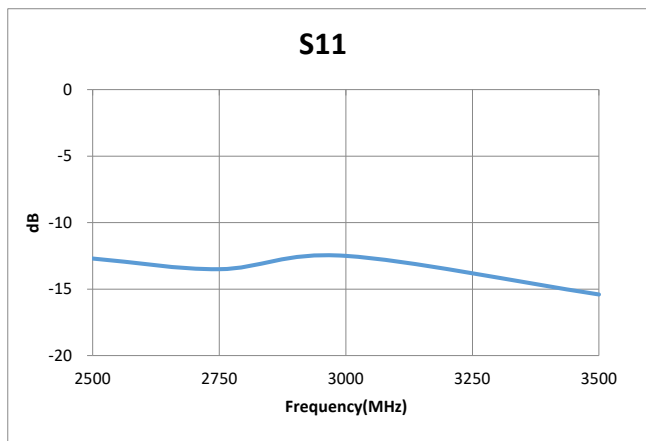
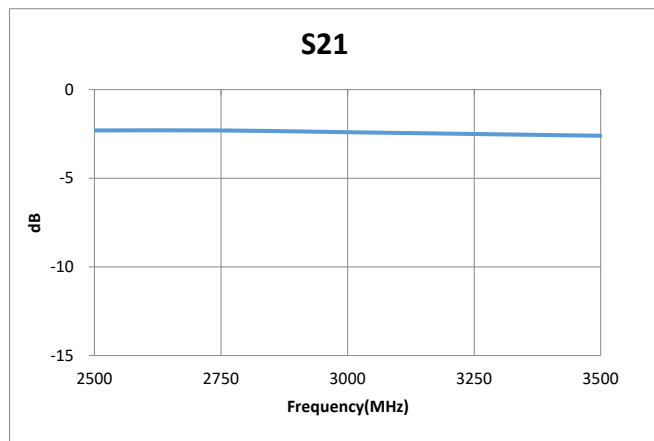
典型性能曲线(VDD=+5V、2500MHz-3500MHz)

低噪放模式测试条件: VDD = +5V, Iq=71mA, LNA ON, Bypass OFF, 50Ω 测试系统。



**典型性能曲线(VDD=+5V、2500MHz-3500MHz)**

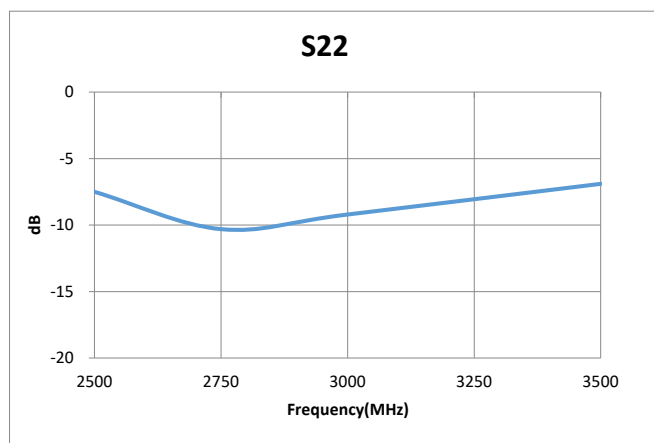
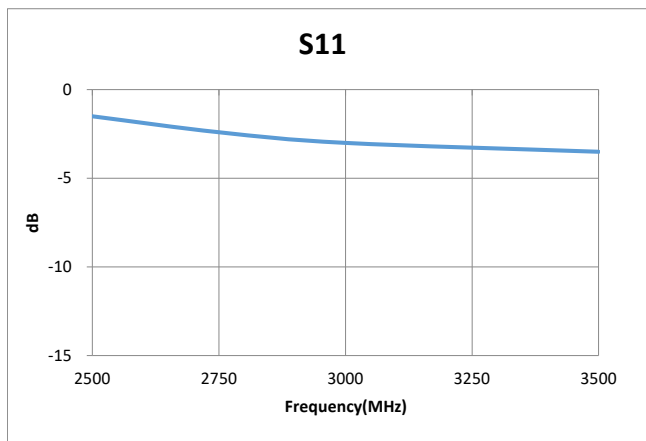
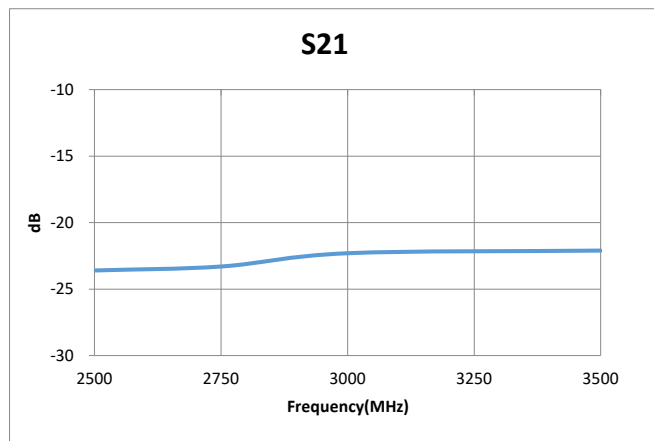
旁路模式测试条件: VDD = +5V, I_q=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。





典型性能曲线(VDD=+5V、2500MHz-3500MHz)

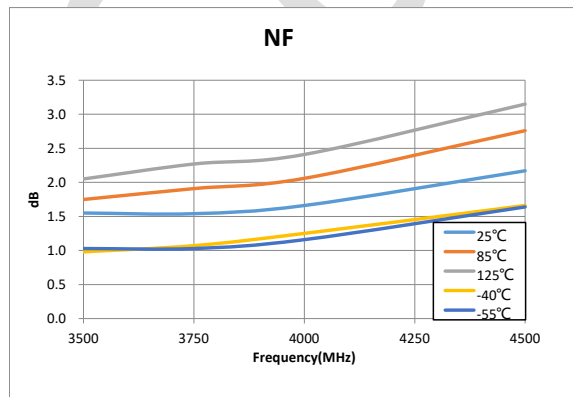
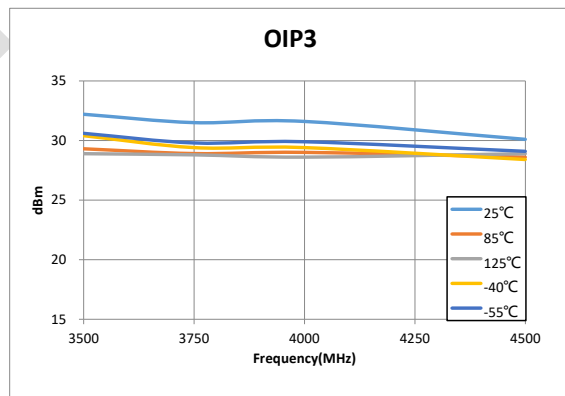
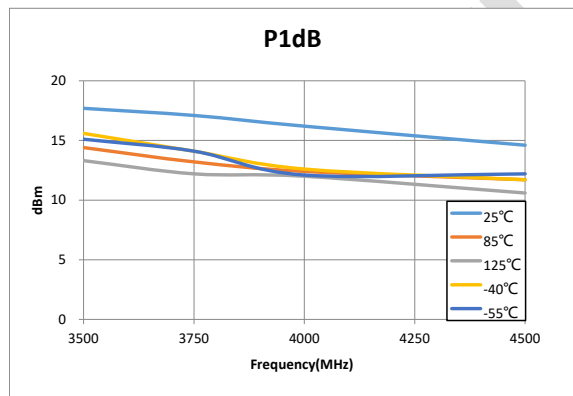
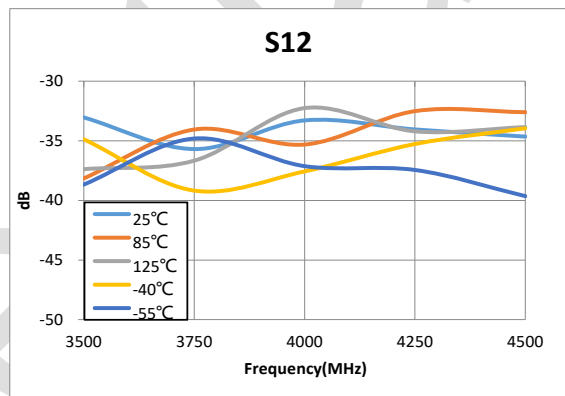
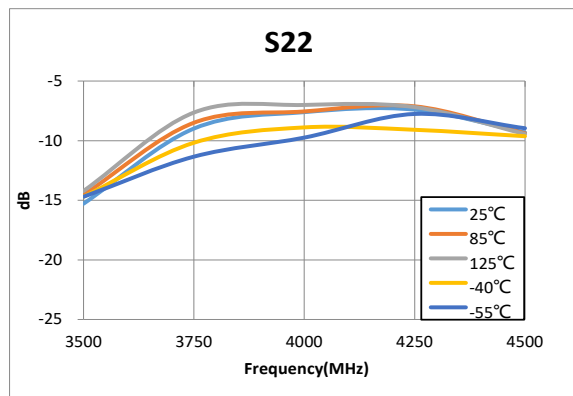
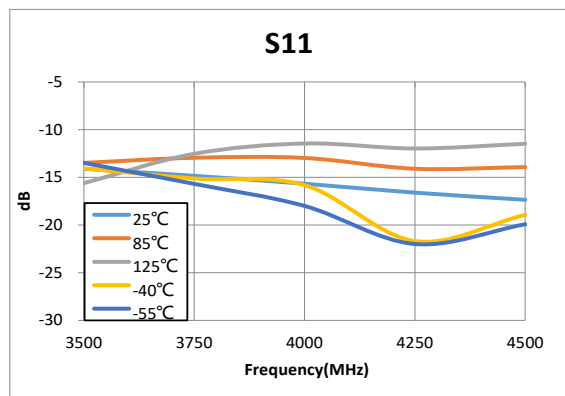
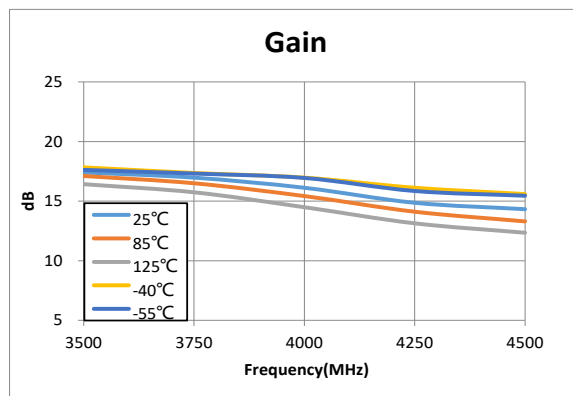
关断模式测试条件: VDD = +5V, I_q=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。





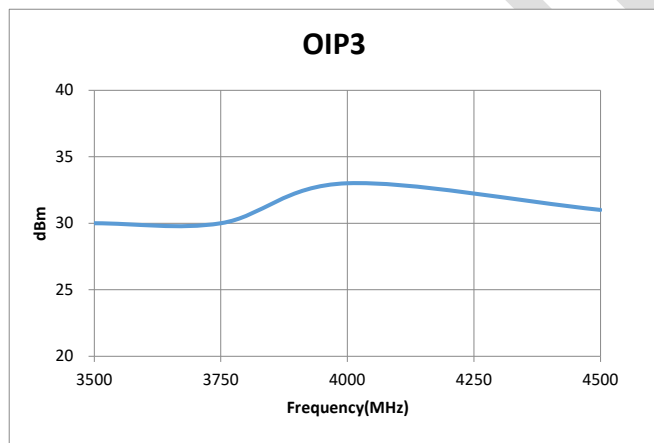
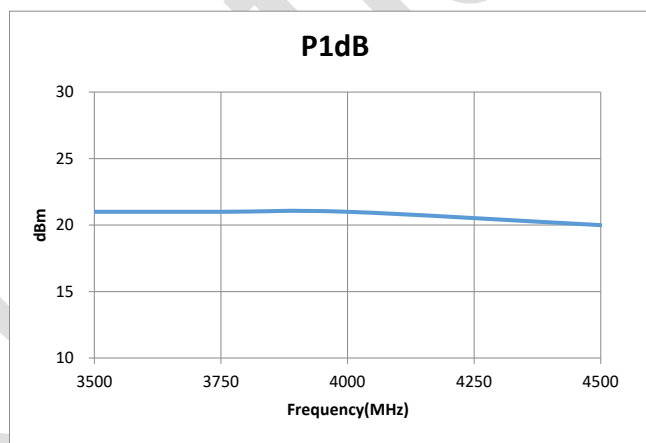
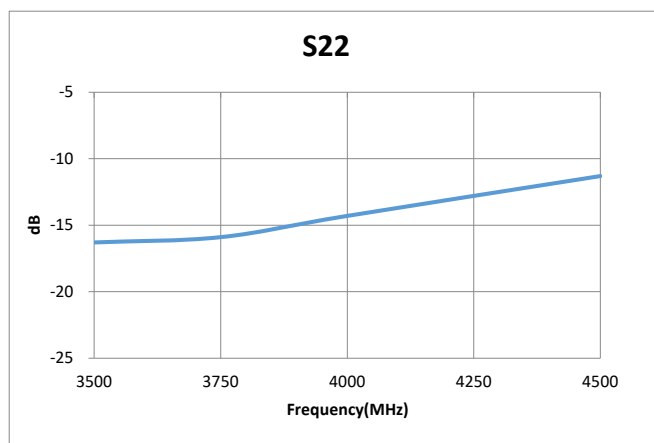
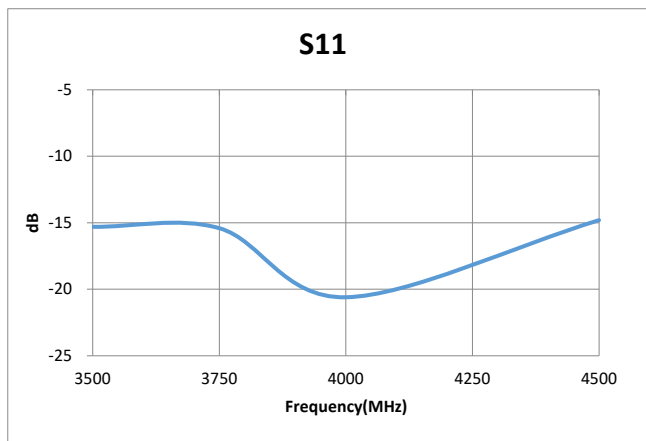
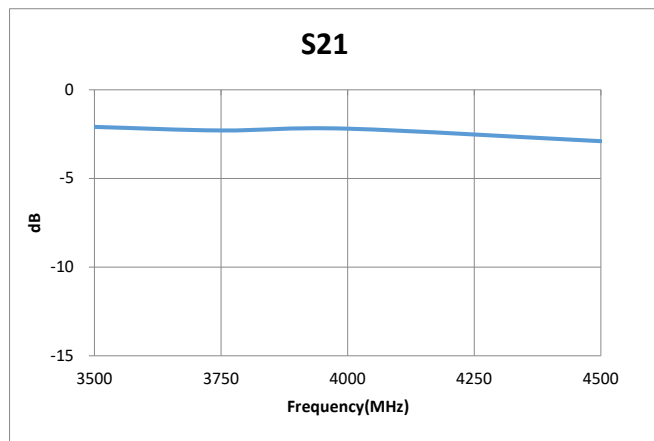
典型性能曲线(VDD=+5V、3500MHz-4500MHz)

低噪放模式测试条件: VDD = +5V, Iq=75mA, LNA ON, Bypass OFF, 50Ω 测试系统。



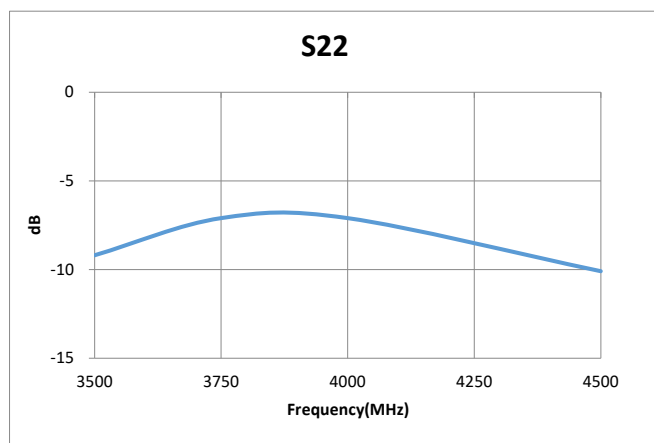
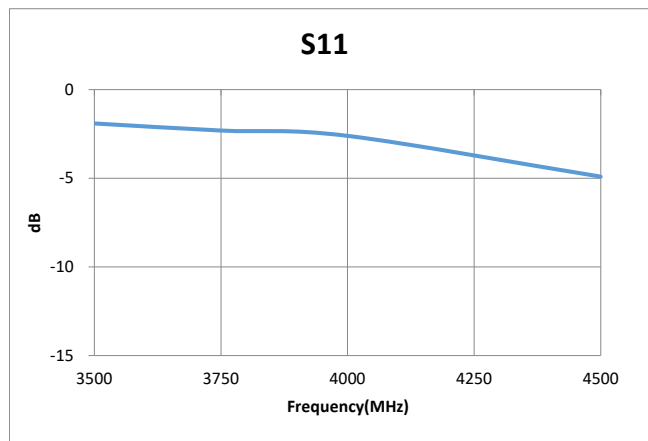
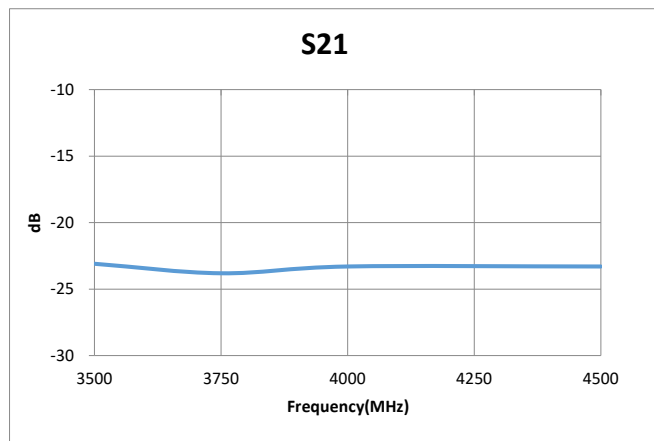
**典型性能曲线(VDD=+5V、3500MHz-4500MHz)**

旁路模式测试条件: VDD = +5V, Iq=8mA, LNA OFF, Bypass ON, Temp= 25°C, 50Ω 测试系统。



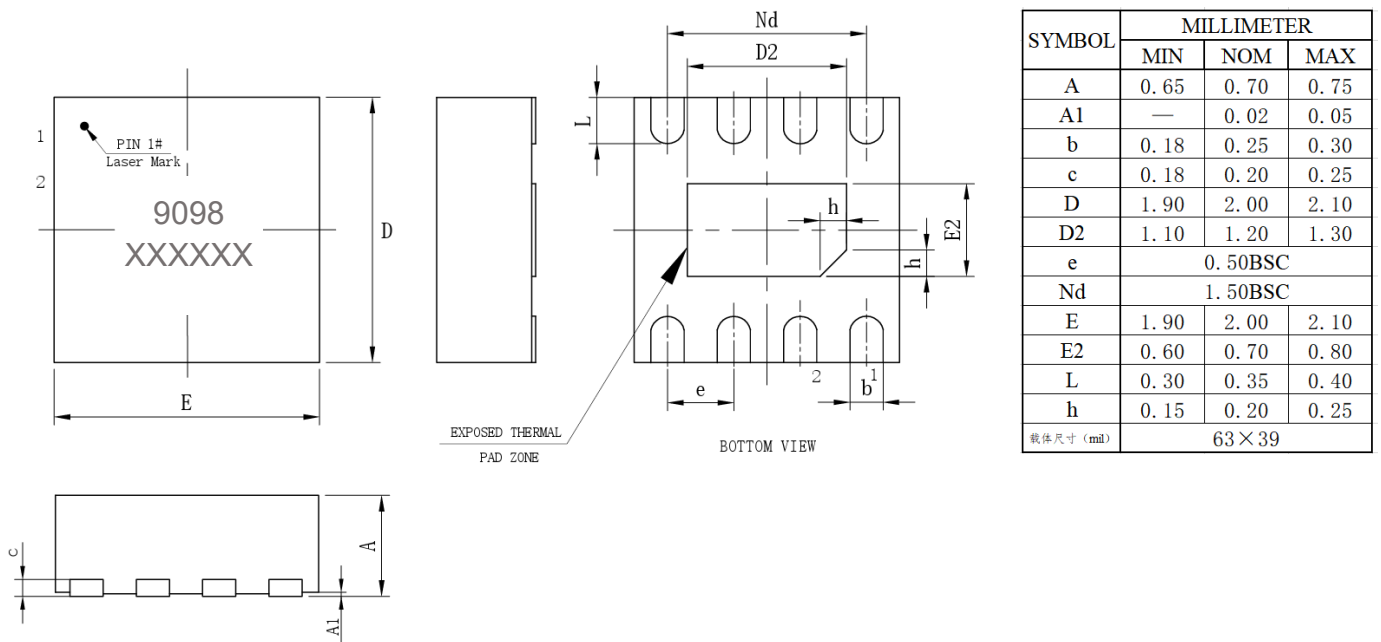
典型性能曲线(VDD=+5V、3500MHz-4500MHz)

关断模式测试条件: VDD = +3.3V, Iq=5mA, LNA OFF, Bypass OFF, Temp= 25°C, 50Ω 测试系统。





封装尺寸图



订单信息

型号	丝印	封装
ZDH9098	9098	DFN2x2-8